

ELECTRON MICROSCOPY

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徐統

2009-3-5

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References:

- Optics, in any standard freshman or high school physics course.
- "Transmission Electron Microscopy" D.B. Williams and C. B. Carter, 1996, Plenum.
- "Scanning Electron Microscopy and X-ray Microanalysis" J.I. Goldstein, D.E. Newbury, P. Echin, D.C. Joy, C.E. Lyman, E. Lifshin, L. Sawyer, and J.R. Michael, 3rd ed, 2003, Kluwer/Plenum.
- "Diffraction Physics" J.M. Cowley, 3rd ed, 1995, North-Holland.
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- "Practical Electron Microscopy in Materials Science" J. W. Edington, 1976, Van Nostrand Reinhold.
- "Procedures in Electron Microscopy", eds. A.W. Robards and A.J. Wilson, 1996 (or later), Wiley.
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- "DigitalMicrograph", Gatan, Inc.

Outline:

Introduction

The Electron microscope

Principle of image formation

Diffraction

Specimen preparation

Contrast / Applications

Scanning electron microscopy

Electron microprobe / Analytical electron microscopy

Applications in nano-materials research

Introduction:

Why electron microscopy?

Sensitivity:

Beam/solid (specimen) interaction

(Spatial) Resolution:

Microscopy vs. microprobe

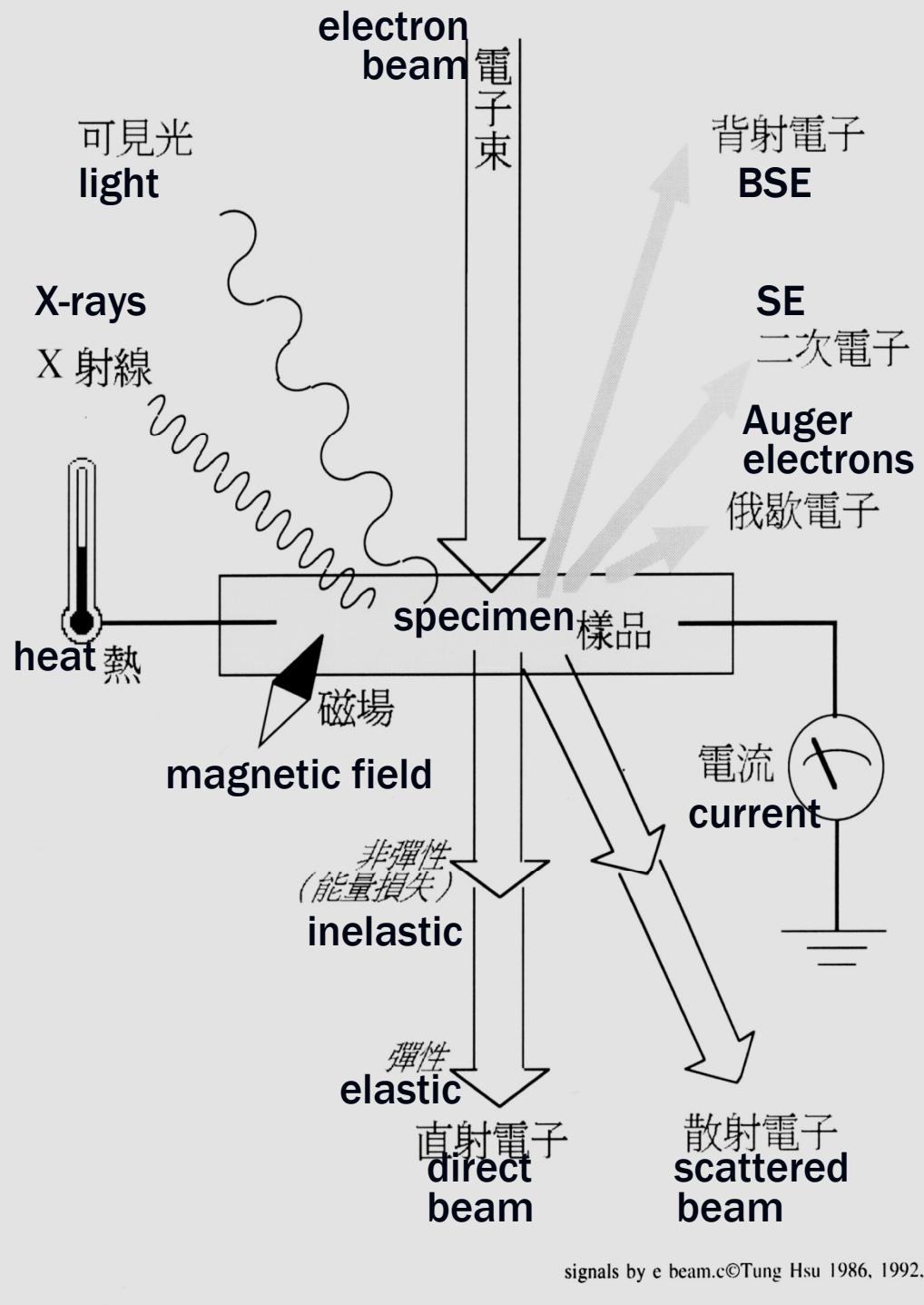
Wavelength, properties of lens

Beam/solid interaction

Information other than the image



Traditional materials
characterization:
incidence beam (probe):
photon
exit beam (signal): photon
detector: eye
processor/storage: brain
(ref. Taiyo)



Why electron microscopy (EM)?

Information obtainable from EM

Beam/solid interaction

image: morphology

scattering power

crystal structure

crystal defects

atomic structure

other than the image:

(chemical) elemental composition
electronic structure

Microscope or microprobe

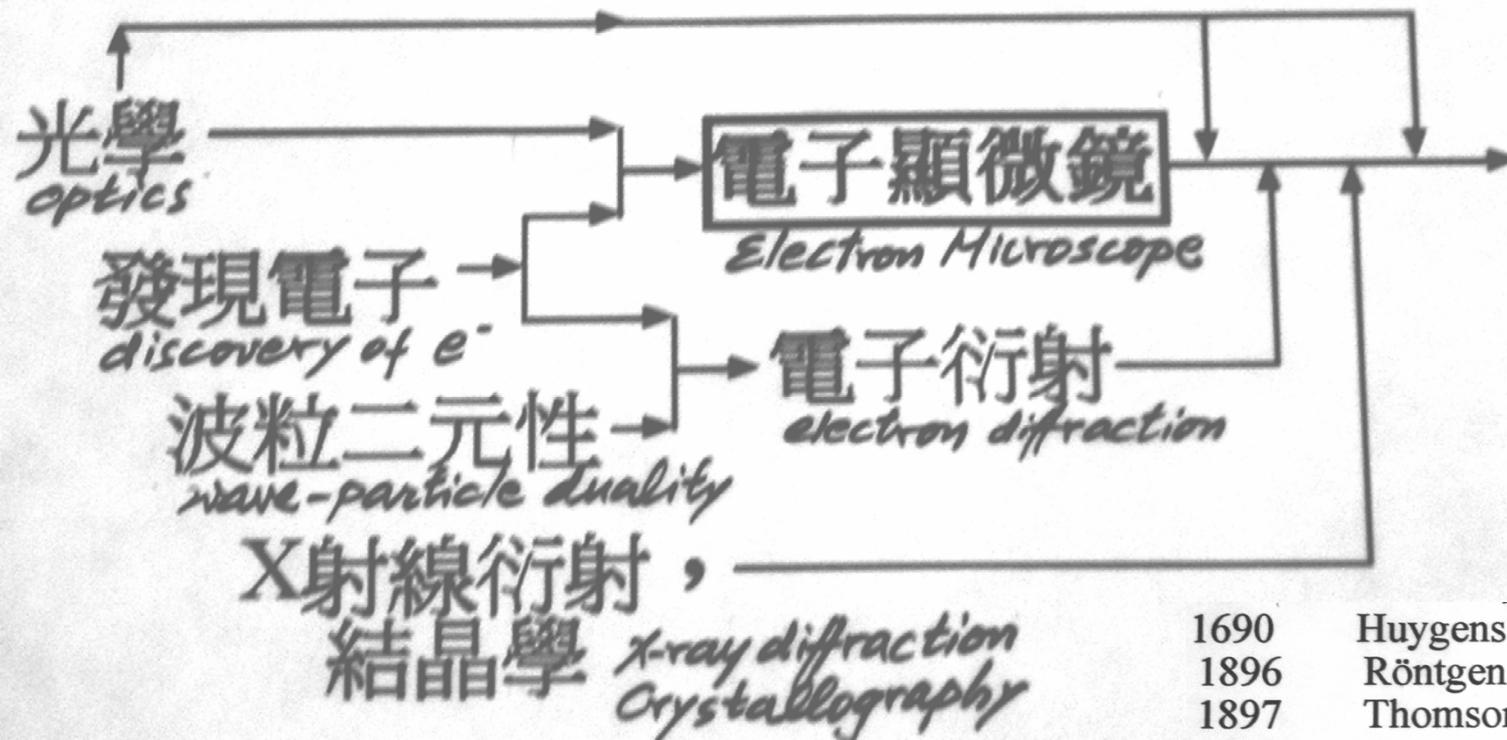
(Spatial) Resolution:

Wavelength, properties of lens

電子顯微鏡的早期歷史

The early history of electron microscopy

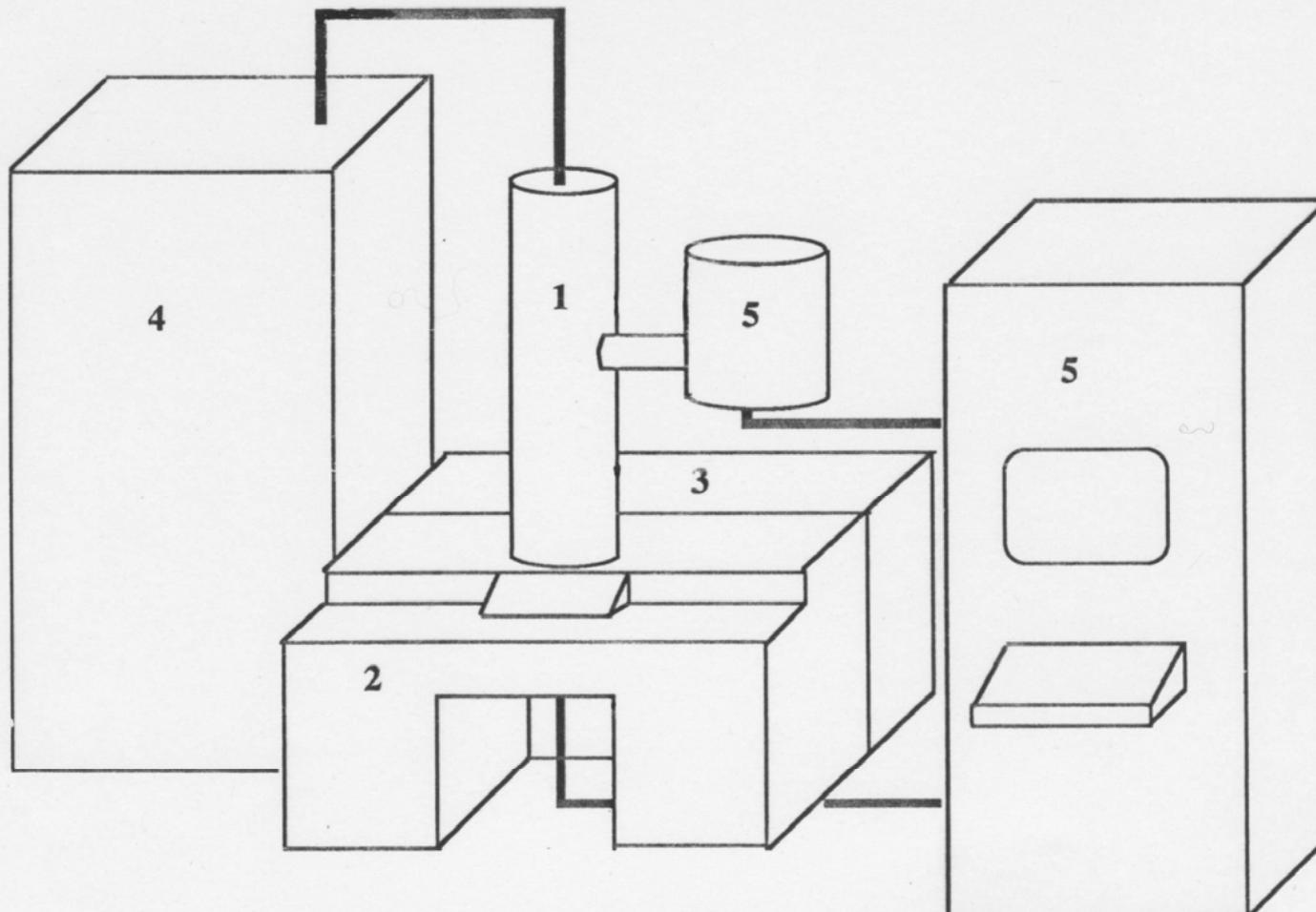
A brief history of electron microscopy



1690	Huygens: 光波，衍射
1896	Röntgen: 發現X射線
1897	Thomson: 發現電子
1913	Bragg and Bragg, von Laue: X射線衍射
1924	de Broglie 波
1926	Schödinger 方程式
1927	Busch: 電子束聚焦
1931	Davisson & Germer, Thomson: 電子衍射
1934	Ruska & Knoll: 鐵心磁鏡 完成電子顯微鏡

Various Electron Microscopes

(vg)



MAJOR COMPONENTS OF A TEM

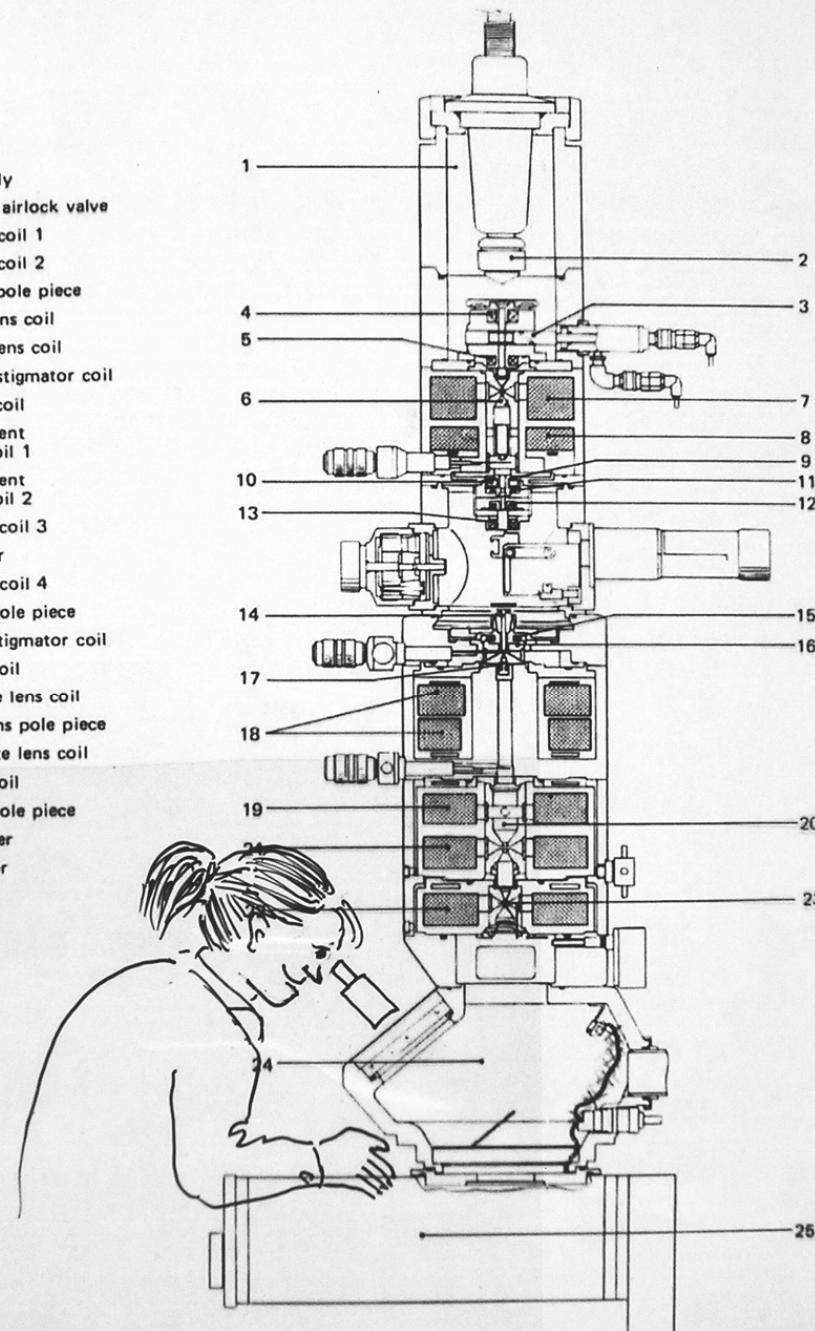
1. electron optics column
2. electronics and controls
3. vacuum system
4. high voltage power supply
5. accessories

透镜
电子系统
真空系统
高压电源
附件

The Electron microscope

Structure and major components

1. Anode chamber
2. Cathode assembly
3. Anode chamber airlock valve
4. Beam deflector coil 1
5. Beam deflector coil 2
6. Condenser lens pole piece
7. 1st condenser lens coil
8. 2nd condenser lens coil
9. Condenser lens stigmator coil
10. Image wobbler coil
11. Beam displacement compensating coil 1
12. Beam displacement compensating coil 2
13. Beam deflector coil 3
14. Specimen holder
15. Beam deflector coil 4
16. Objective lens pole piece
17. Objective lens stigmator coil
18. Objective lens coil
19. 1st intermediate lens coil
20. Intermediate lens pole piece
21. 2nd intermediate lens coil
22. Projector lens coil
23. Projector lens pole piece
24. Viewing chamber
25. Camera chamber



The Electron Optics Column of JEOL JEM-100C (vg)

The Lens System:
Condenser Lens:
Controls beam intensity, density, convergence, coherence.

Objective Lens:
Magnification, introducing contrast.

Intermediate Lens:
Further magnification, imaging or diffraction.

Projector Lens:
Final magnification

Apertures
Specimen chamber
Camera

The electron gun:

An electrostatic lens +
an electron accelerator

Filament: Tungsten
 LaB_6
Field emission

Acceleration voltage:
(HV or HT)
100kV - 1MV

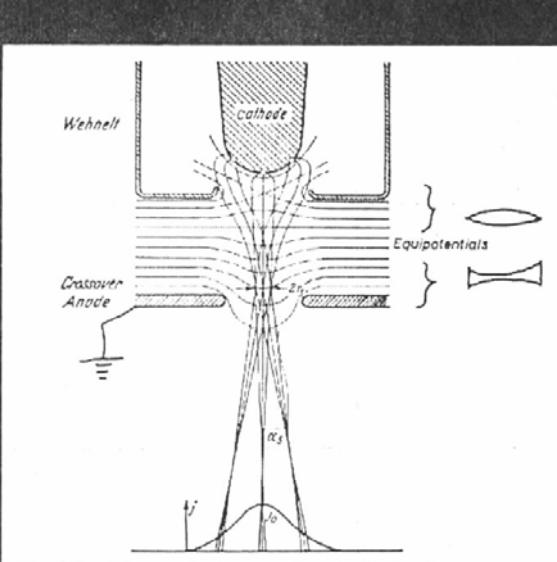


Fig. 3.2. The terminology associated with the electron gun.

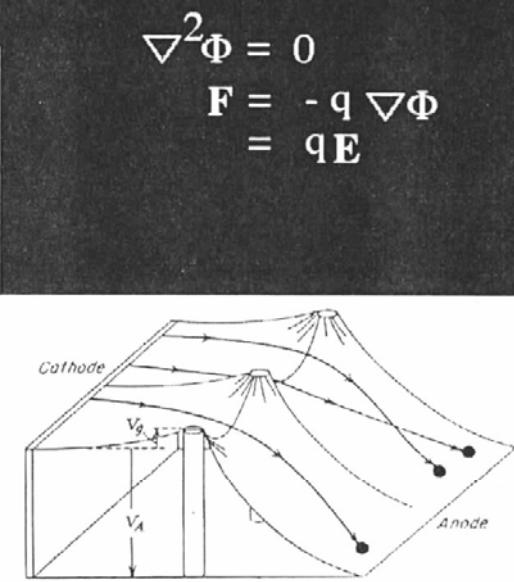


Fig. 2.9. The rubber-membrane model for experimental determination of electron paths (exaggerated vertical scale).

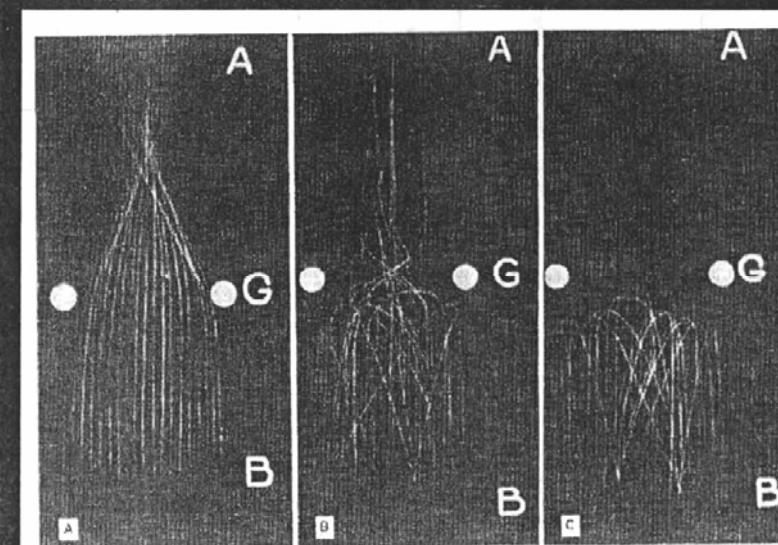
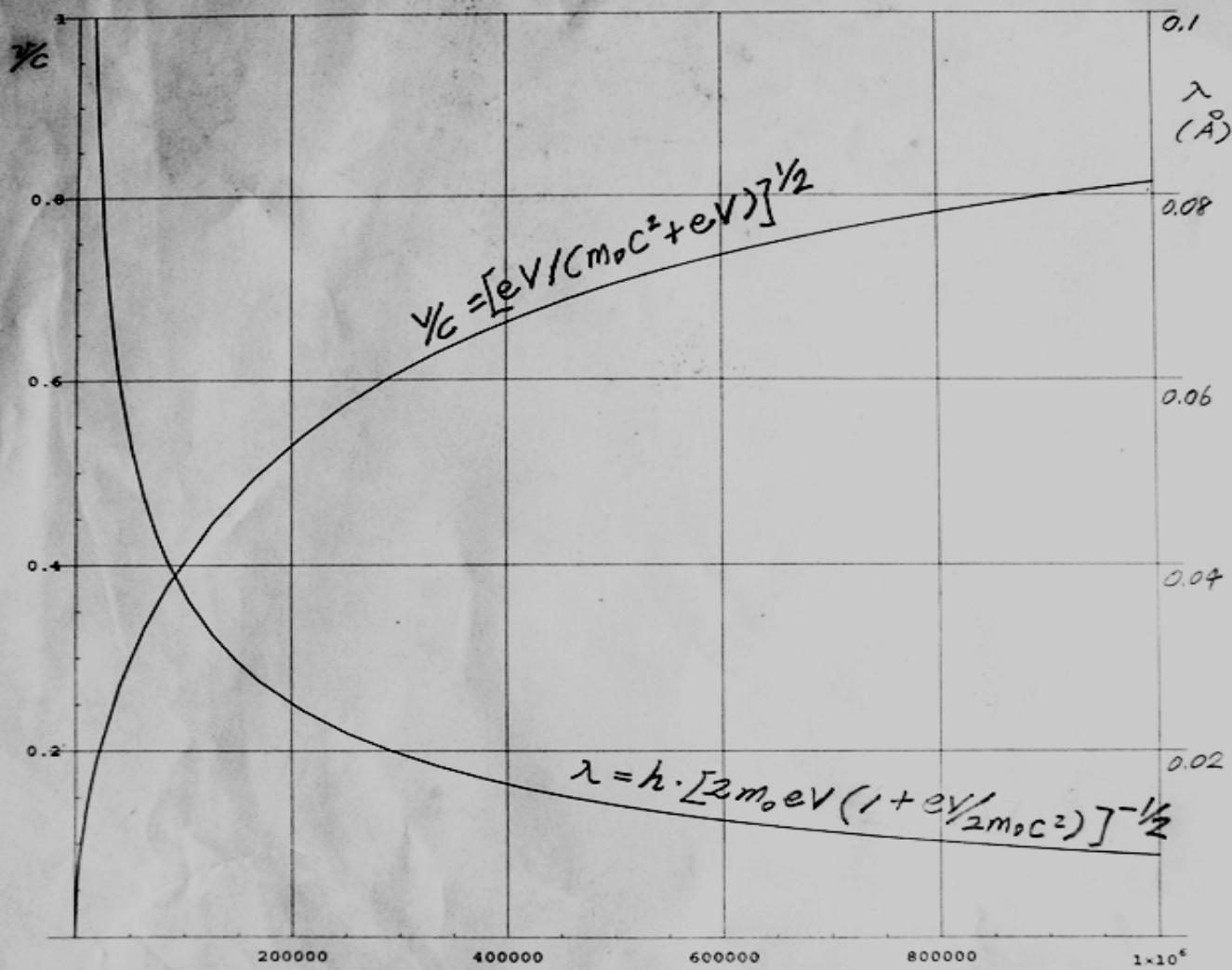


Fig. 2.10. Electron paths in a triode as determined with the rubber-membrane model. A is the anode, B the cathode, and G the grid. The grid potential is increasingly negative from A to C. (Courtesy Philips Tech. Rev., Ref. 2.)



e : electron charge

v : " velocity

V : acceleration voltage

m_0 : electron rest mass

c : speed of light in vacuum

h : Planck's constant

λ : electron wavelength

(eV)

The electromagnetic lens

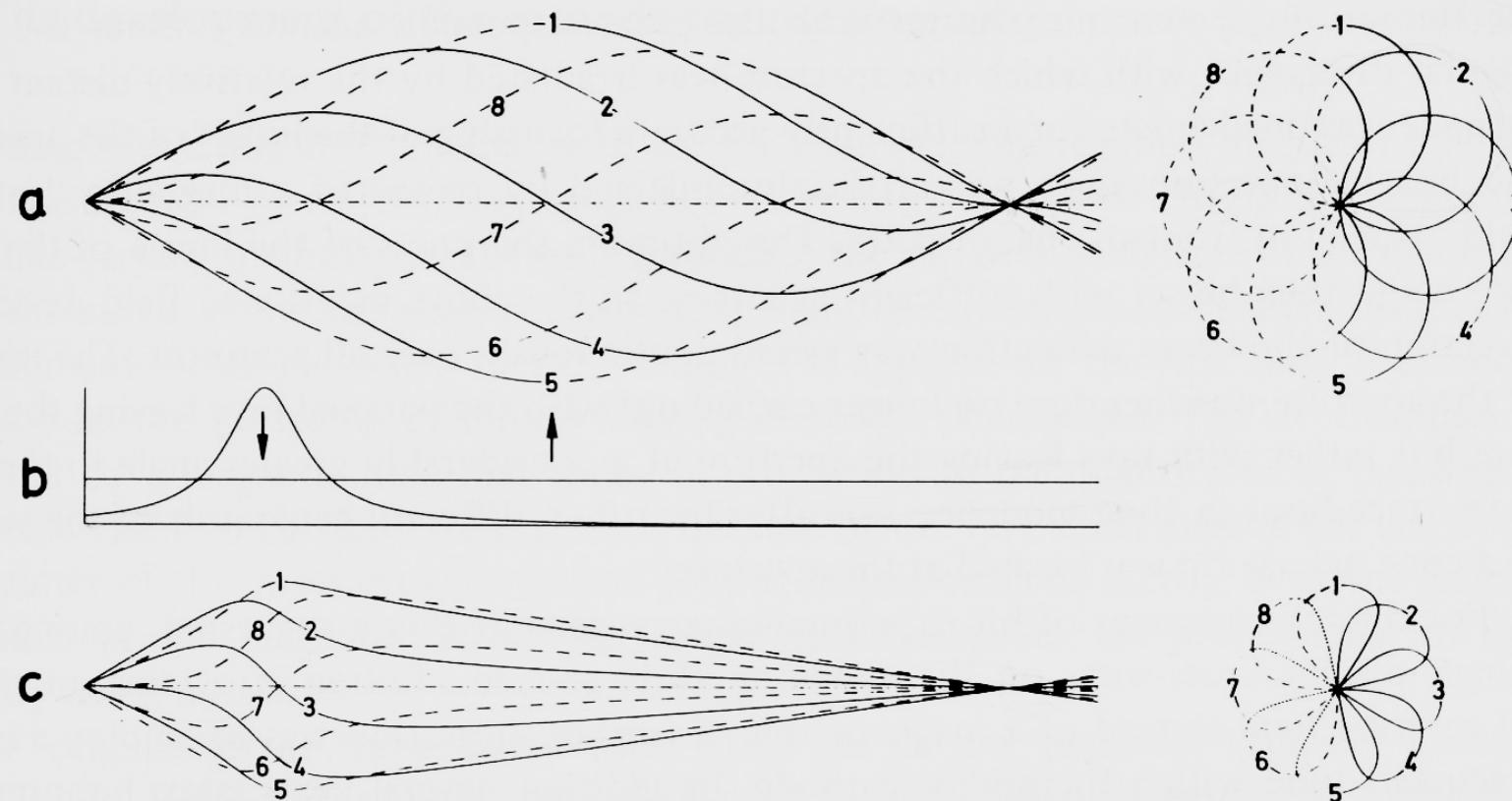
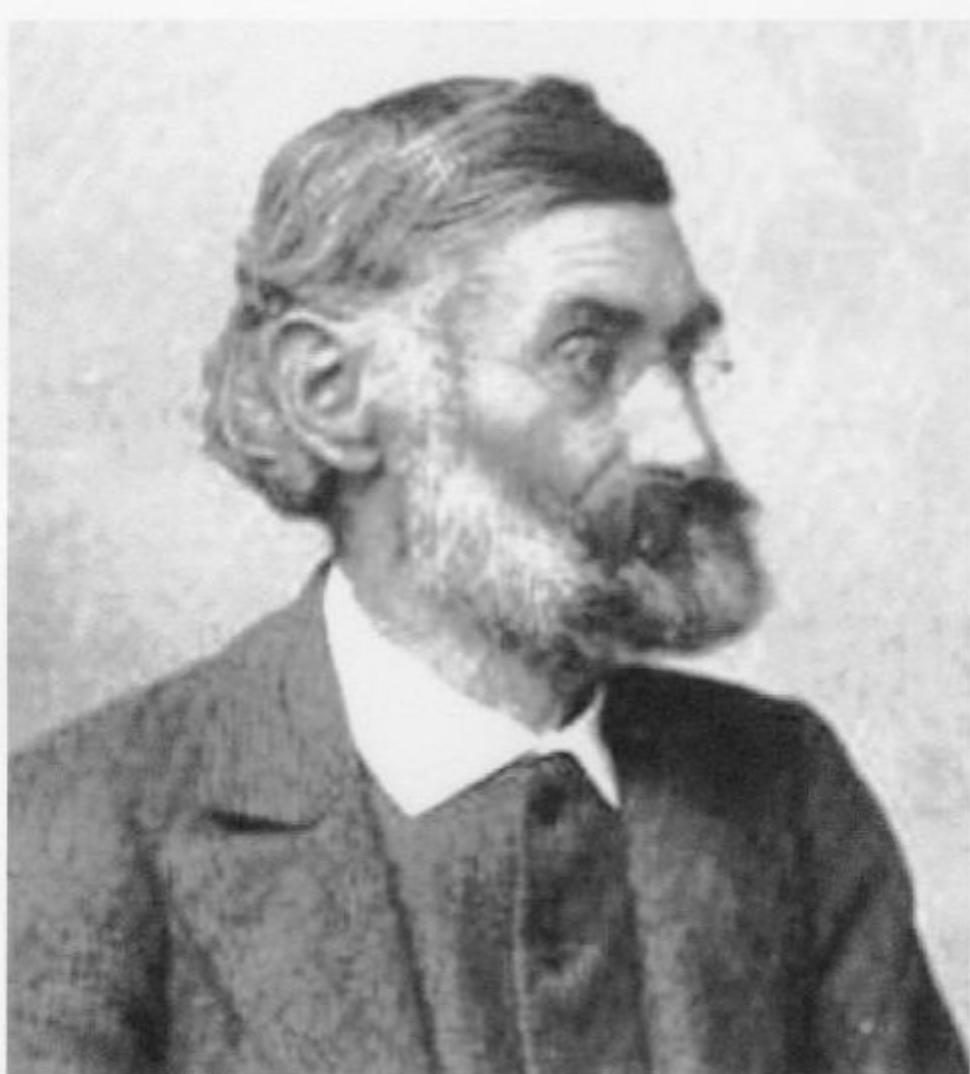


Fig. 1. Electron trajectories in a uniform (a) and in a non-uniform (c) magnetic field, issuing from an axial point of the specimen for different azimuth angles, but making the same angle with the lens axis. (b) Field distributions corresponding to (a) and (c).

"The early development of electron lenses and electron microscopy",
Ernst Ruska, 1980, S. Hirzel Verlag Stuttgart



Ernst Abbe
1840-01-23 ~ 1905-01-14

JOC/EFR September 2003

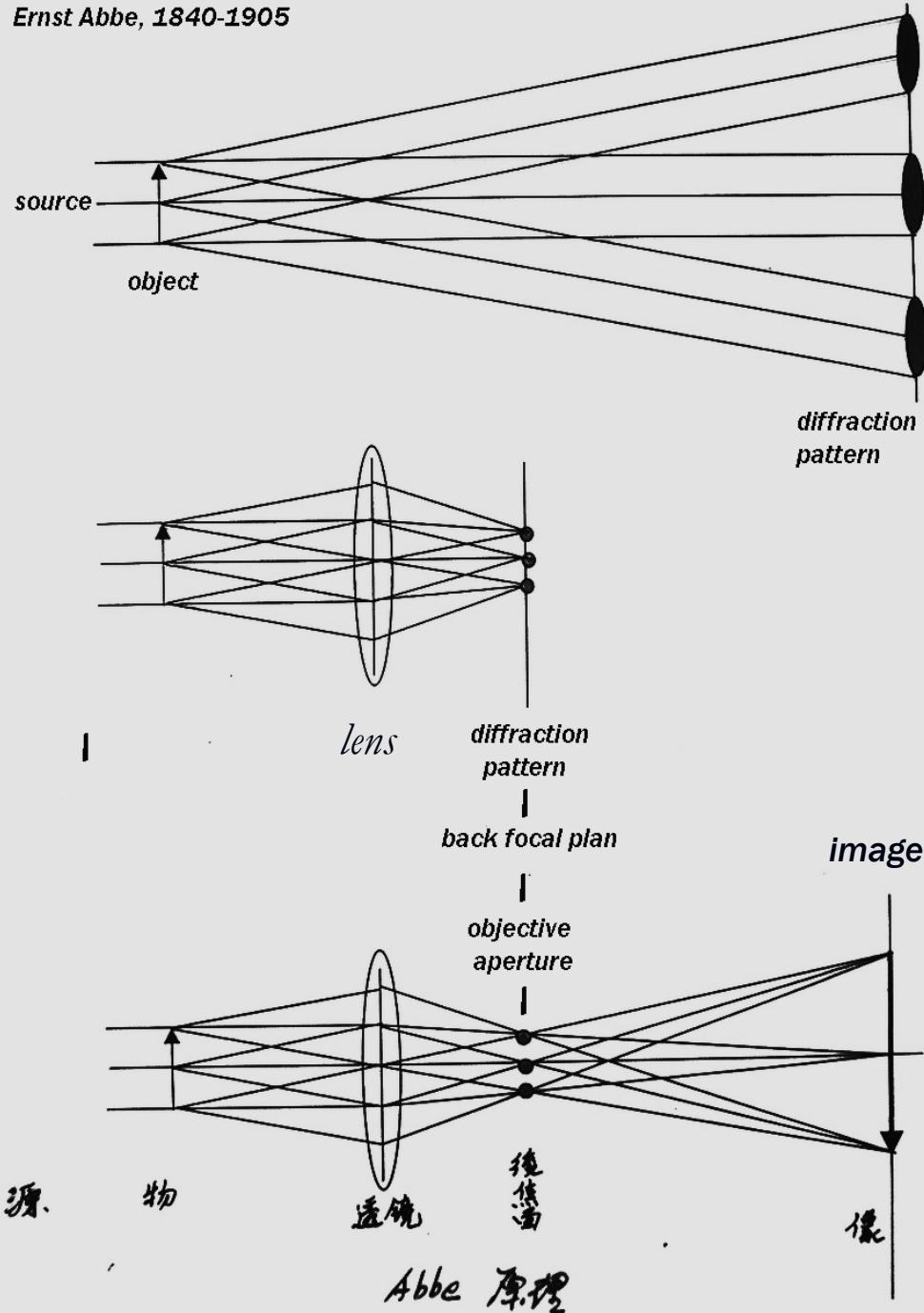
The URL of this page is:
<http://www-history.mcs.st-andrews.ac.uk/PictDisplay/Abbe.html>

ABBE'S PRINCIPLE

Ernst Abbe (1840-1905),
Carl Zeiss Lab

Copyright
information

Abbe's principle of imaging
Ernst Abbe, 1840-1905



Abbe's Principle of image formation

Principle of Fundamental geometrical and physical optics

Abbe's principle and the back focal plan (BFP)

Contrast: Beam/solid interaction

BFP and the objective aperture:

Bright field (BF)

Dark field (DF) images.

Principle of image formation

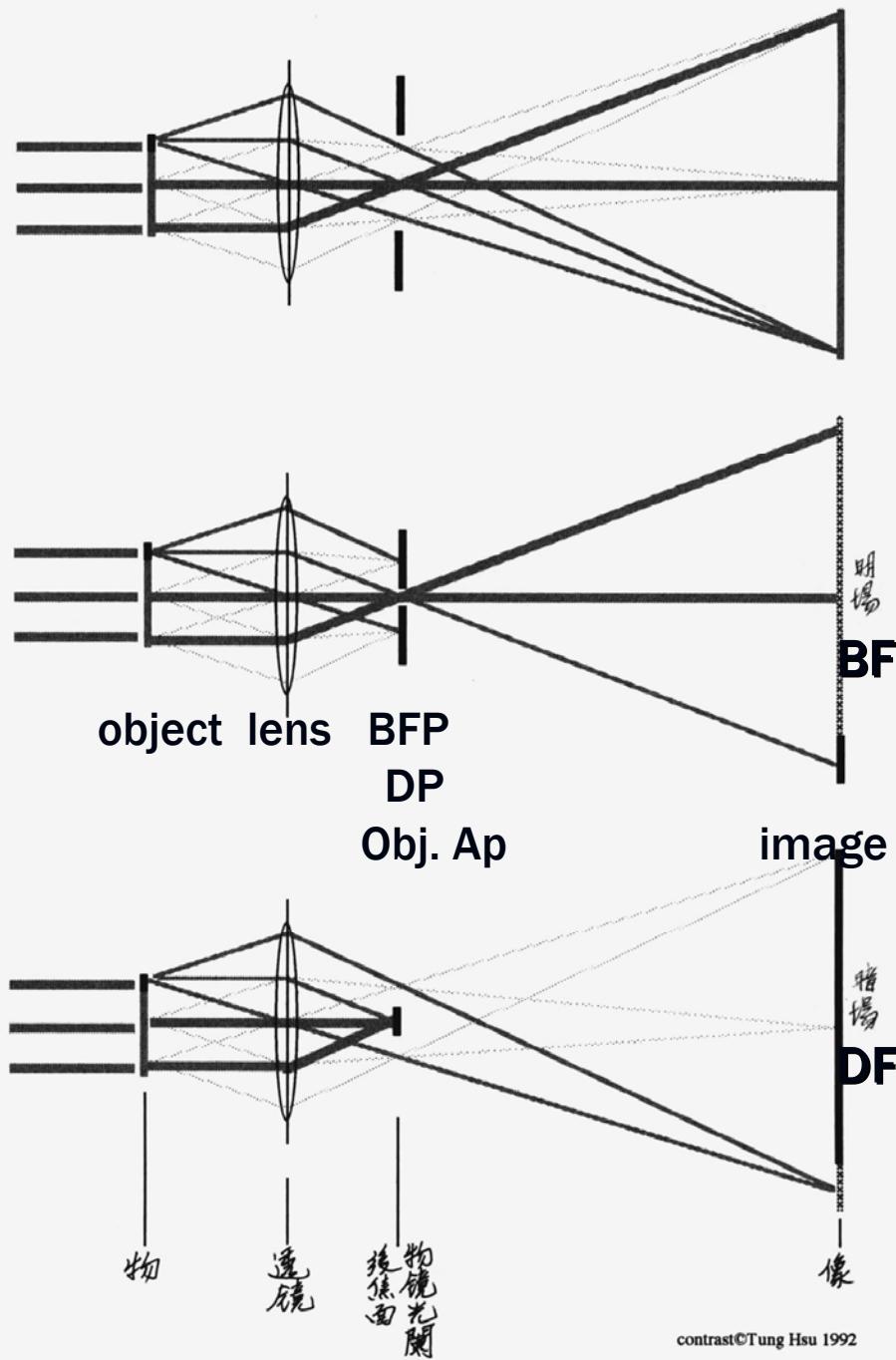
Fundamental geometrical and physical optics

Abbe's principle and the back focal plan (BFP)

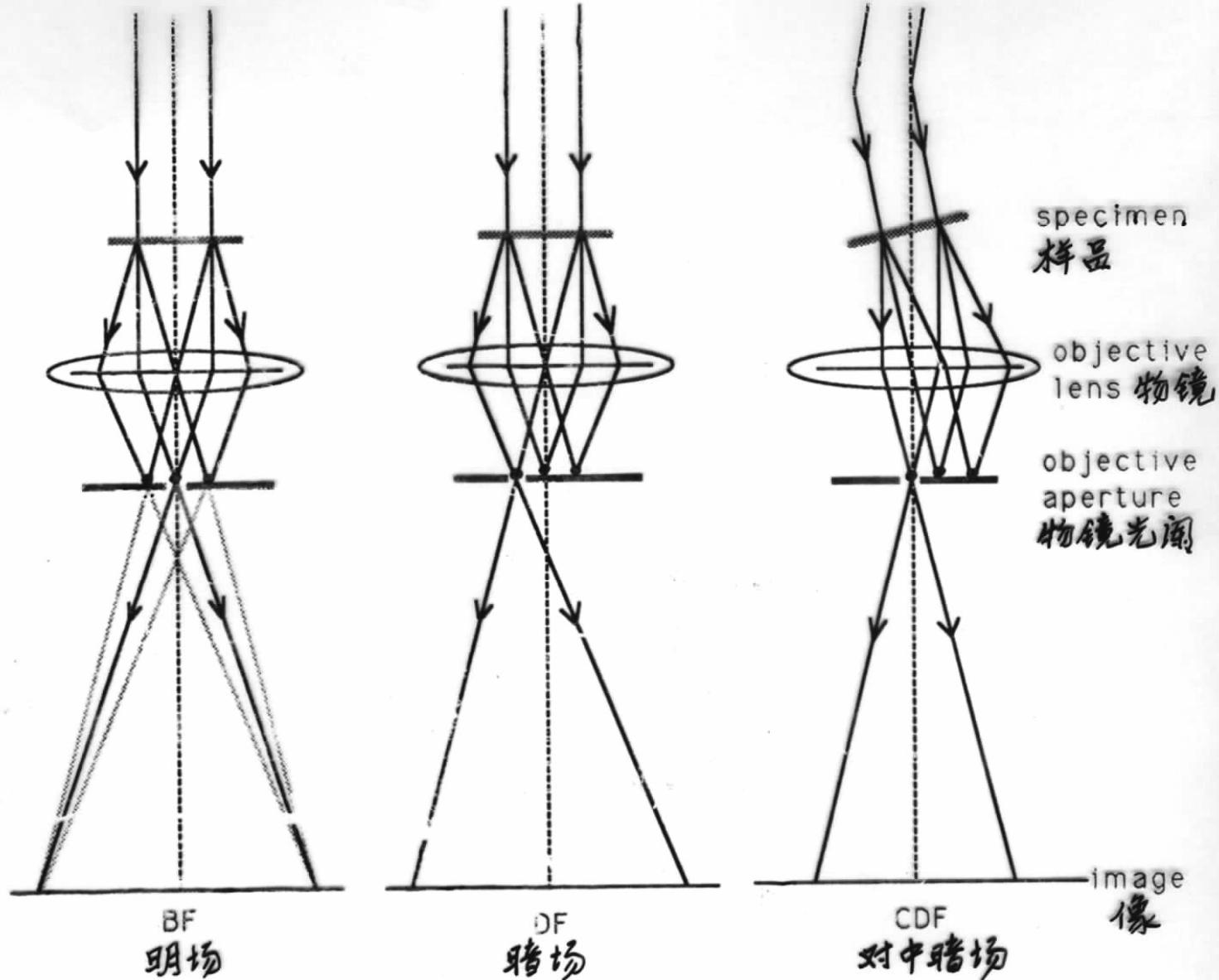
Contrast: Beam/solid interaction

BFP and the objective aperture:

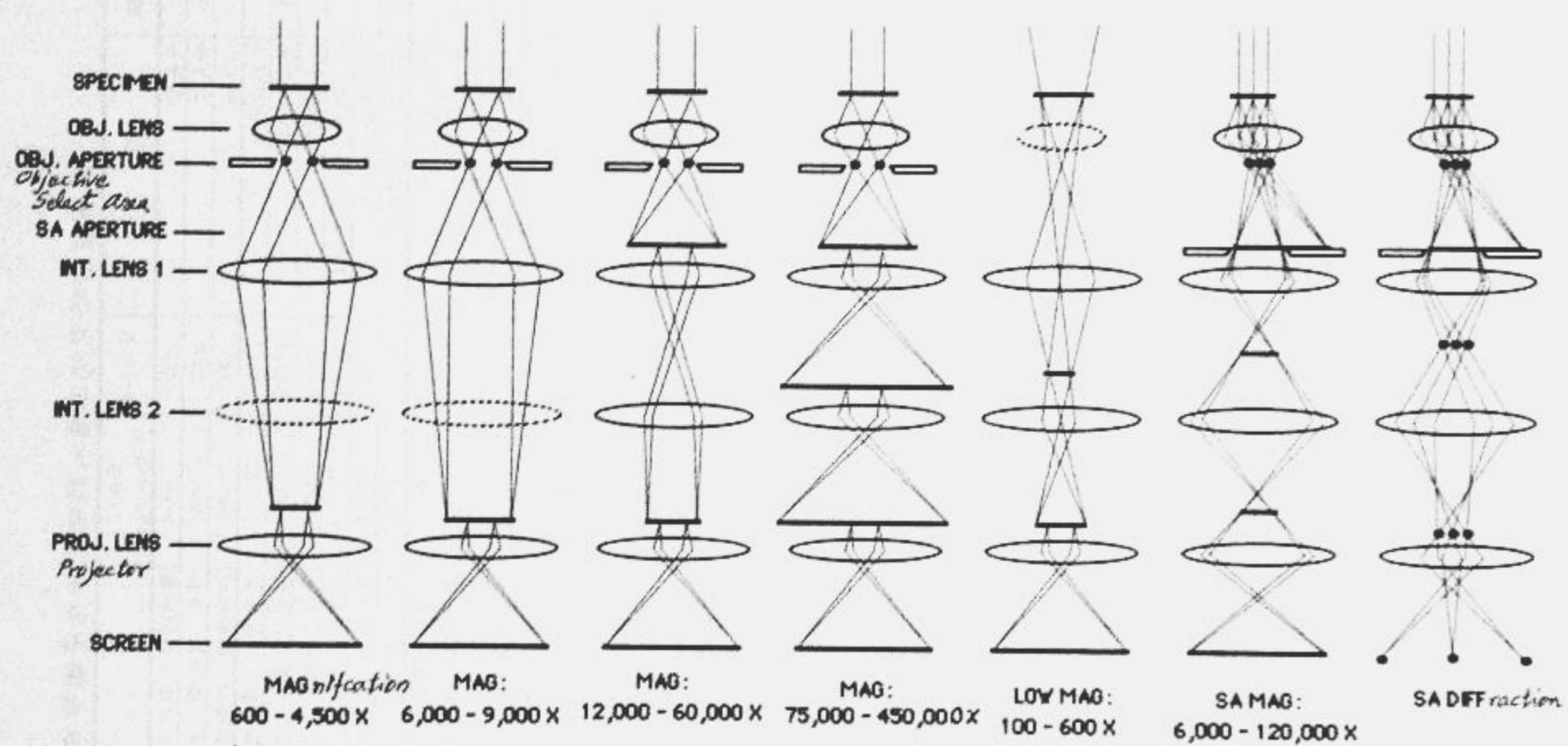
Bright field (BF) and dark field (DF) images.



**Contrast: Beam/solid interaction
BFP and the objective aperture:
Bright field (BF) and dark field (DF)
images.**



DIFFRACTION CONTRAST
繞射襯度 (衍射)



The Electron microscope
operation

diffraction pattern ↑

Electron micrographs
(EM, TEM images)

And

(Transmission) electron diffraction patterns
(TED patterns, DP) (vg)

Diffraction Pattern

Diffraction Contrast

What is Diffraction?

What is DIFFRACTION?

Feynman “Lectures on Physics” Ch. 30. Diffraction

This chapter is a direct continuation of the previous one, although the name has been changed from *Interference* to *Diffraction*. No one has ever been able to define the difference between interference and diffraction satisfactorily. It is just a question of usage, and there is no specific, important physical difference between them. The best we can do, roughly speaking, is to say that when there are only a few sources, say two, interfering, then the result is usually called interference, but if there is a large number of them, it seems that the word diffraction is more often used. So, we shall not worry about whether it is interference or diffraction, but continue directly from where we left off in the middle of the subject in the last chapter.

WAVE PROPAGATION, SCATTERING, AND SUPERPOSITION

Electrons fly through the vacuum = electron wave propagating through the vacuum.

Electrons (electron waves) can be scattered by electrostatic potential of atoms.

When two or more electron waves meet, their amplitudes are added (superposition).

Examples of electron micrographs and (transmission) electron diffraction (TED) patterns

Contrast mechanism:

Beam/specimen interaction

Amplitude and/or phase of the electron waves are altered by the specimen

Properties of lens

Waves (rays) initiated from a point on the object cannot be converged by the lens to a point on the image.

Aperture limitation (“diffraction” related)

Spherical aberration

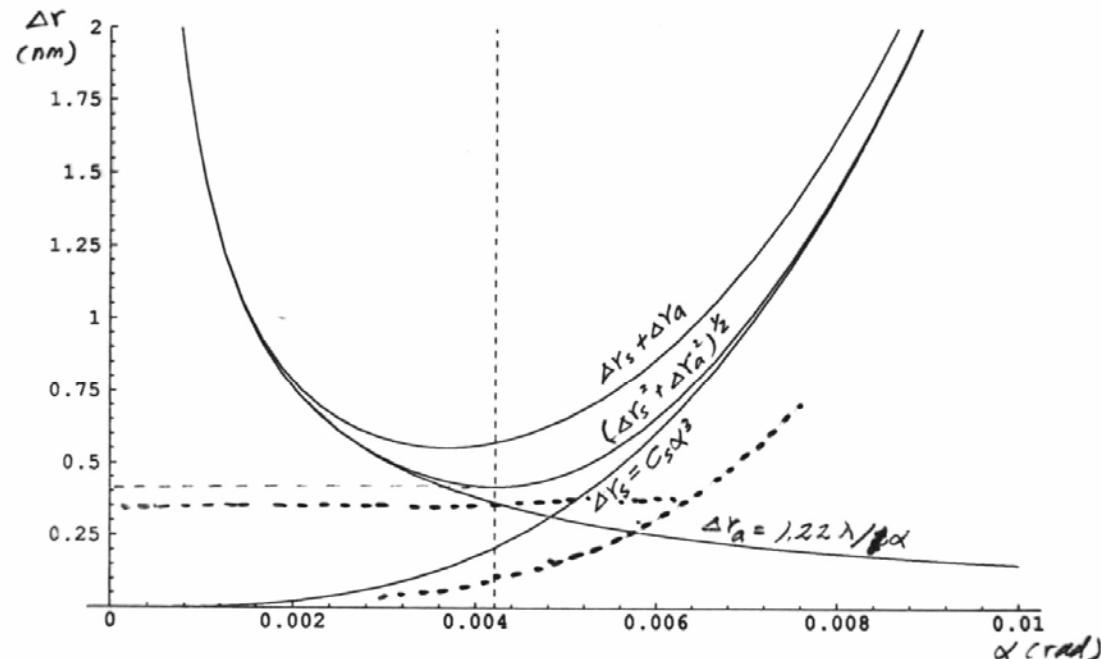
Chromatic aberration

Defocus (“diffraction” related)

Astigmatism

Detector: Fluorescence screen, Film, CCD, eyes

resolution©Tung Hsu 1991
 nm
 $cs=2800000; wl=0.0025; nm$



$$\lambda = \frac{h}{\{2mE(1 + \frac{E}{2mc^2})\}^{1/2}}$$

$$\begin{array}{ll} E = 100 \text{ keV} & \lambda = 0.0027 \text{ nm} \\ 200 \text{ keV} & 0.0025 \text{ nm} \\ 15 \text{ keV} & 0.0099 \text{ nm} \end{array}$$

Fig. 22

$$\lambda = 1.226 [E(1 + 0.9788 \times 10^{-6}E)]^{-1/2} \text{ nm}$$

volt

RESOLUTION:

Rayleigh's criterion

Balancing the spherical aberration effect and the diffraction effect:

Smaller aperture produces larger Airy disc (diffraction pattern of the aperture).

Larger aperture produces more diffused disc due to spherical aberration

Specimen preparation –

Specimen: What characterization is all about.

the ultimate limit of resolution and detectability

General requirements:

thin, small, conductive, firm, dry

Various methods

Ultramicrotomy

Mechanical

Chemical

Ion

(Lucky for nano-materials work: Minimal preparation)

Contrast enhancement:

Staining, evaporation, decoration

Specimen support and specimen holders

Specimen support

Grid

Holey carbon grid

Specimen holders:

Top entry

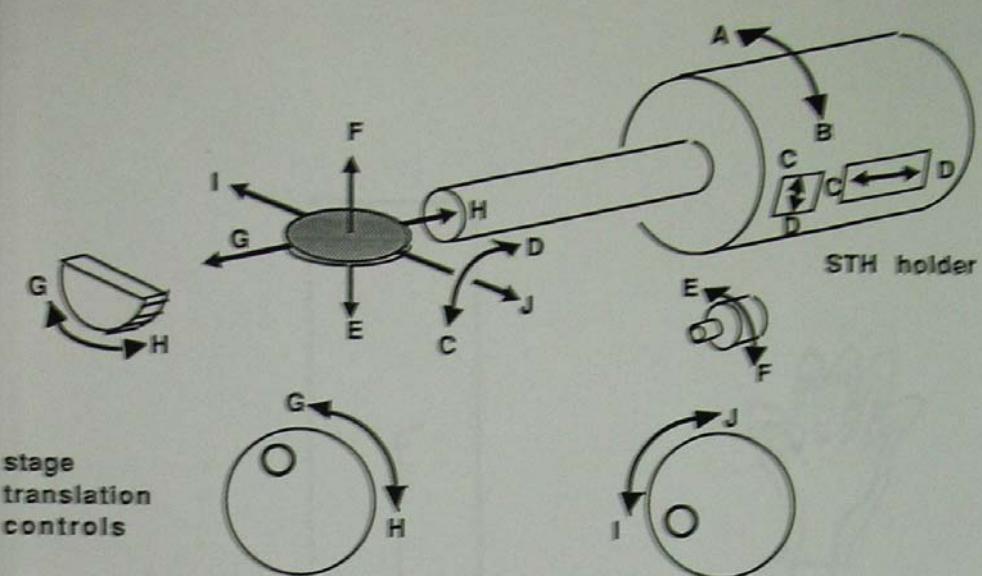
Side entry

Single/double tilt

Heating, cooling, tensile, environmental, etc.

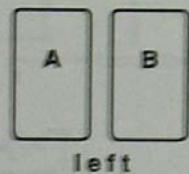
Performance:

Tilt angle, working distance,

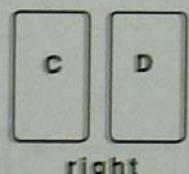


stage
translation
controls

foot pedals



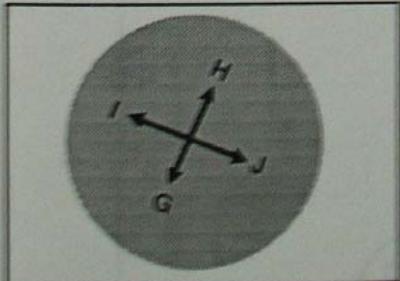
left



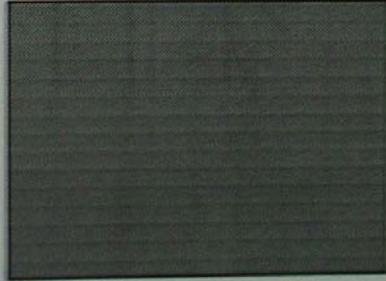
right

A: +1st tilt.	F: +z.
B: -1st tilt.	G: +x.
C: +2nd tilt.	H: -x.
D: -2nd tilt.	I: +y.
E: -z.	J: -y.

specimen



specimen



Movements and controls
of the specimen

WHY VACUUM (LOW PRESSURE)?

Specimen
Filament
Mean free path
of electrons

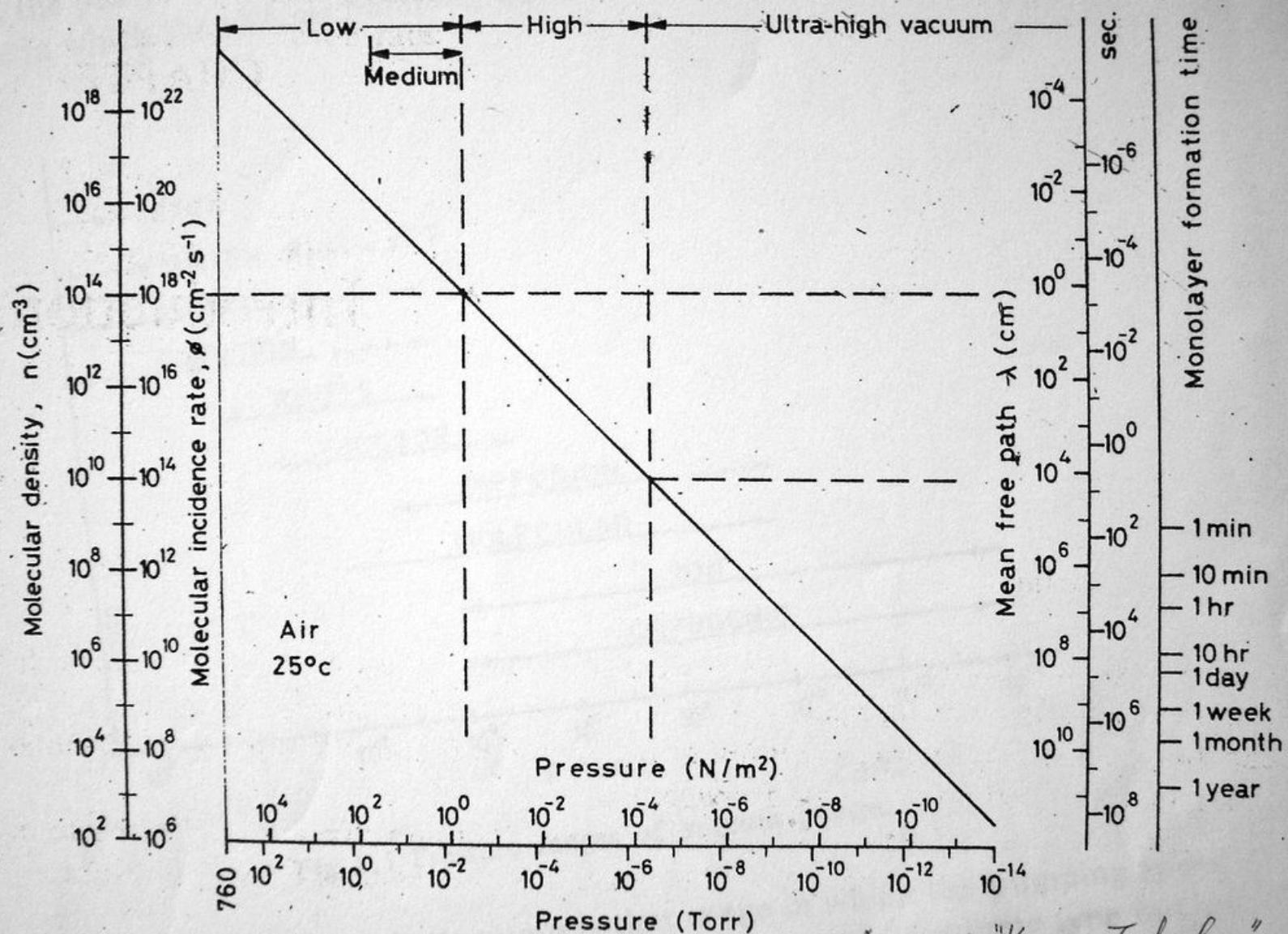
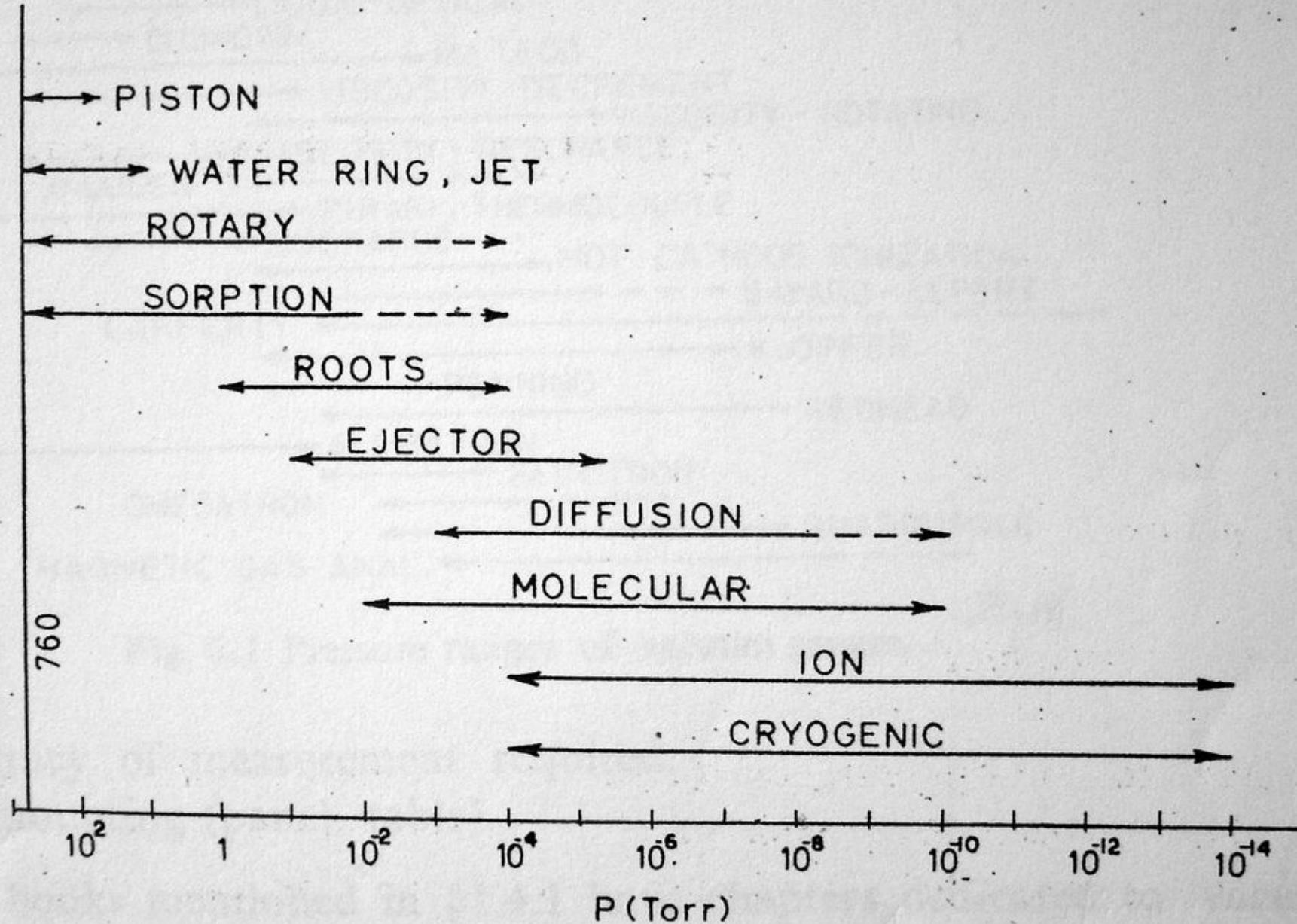


Fig. 1.1 Relationship of several concepts defining the degree of vacuum.
A. Roth "Vacuum Technology"
2nd ed. 1982 North Holland

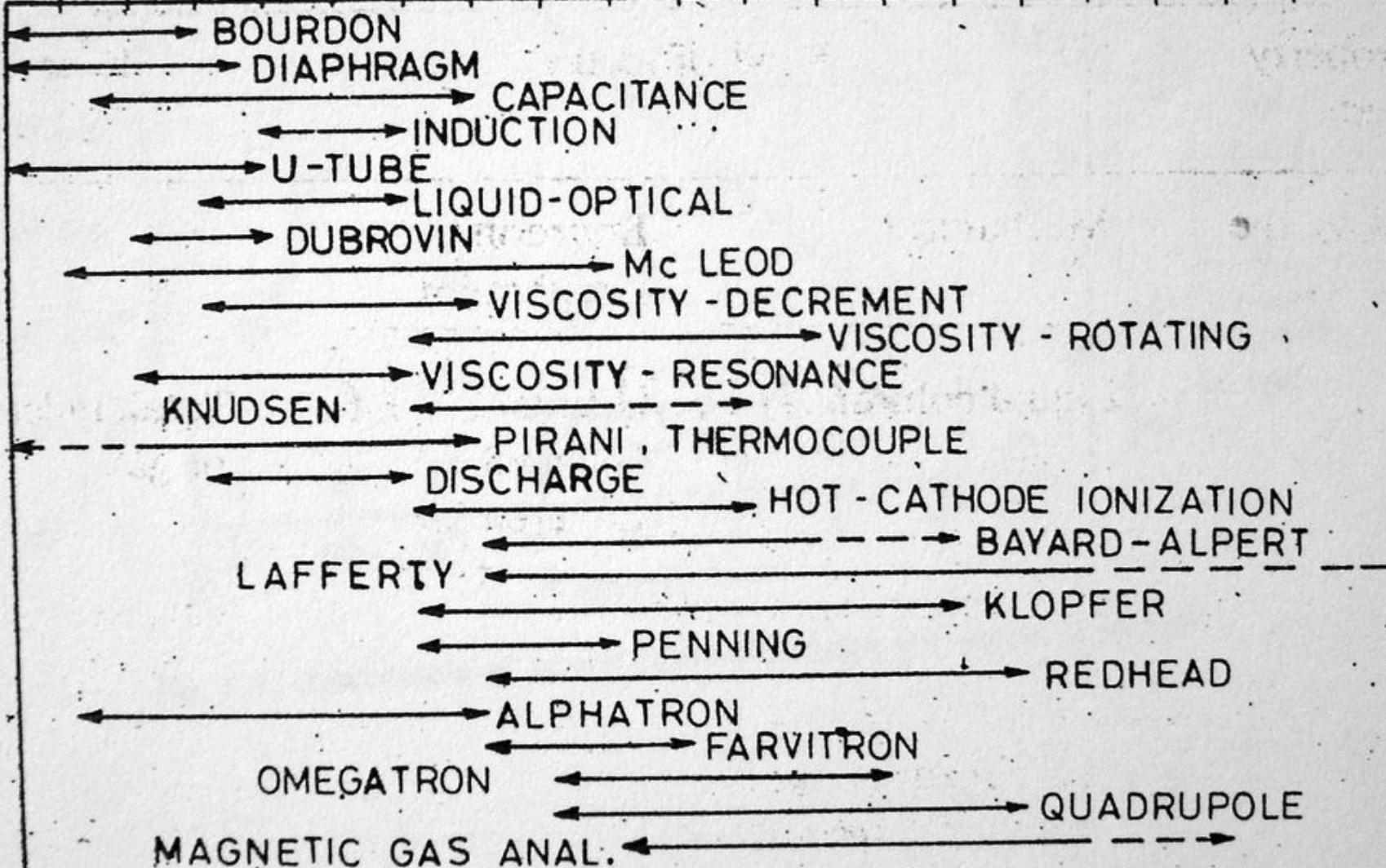


Roth

Fig. 5.1 Pressure ranges of vacuum pumps.

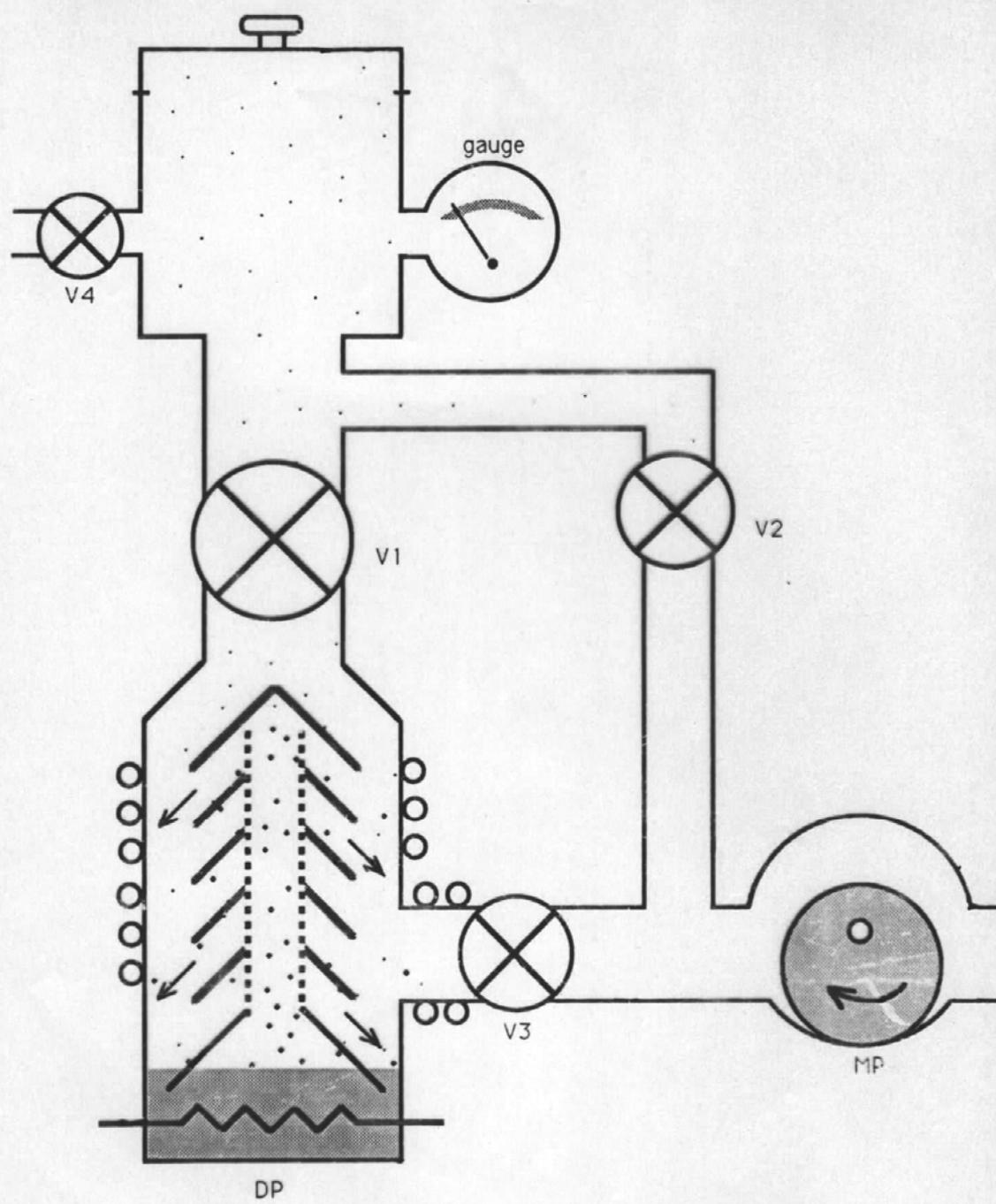
P R E S S U R E (T O R R)

10^2 10^0 10^{-2} 10^{-4} 10^{-6} 10^{-8} 10^{-10} 10^{-12} 10^{-14} 10^{-16}



Roth

Fig. 6.1 Pressure ranges of vacuum gauges.



High Resolution Electron Microscopy (HREM):

Approaching atomic resolution.

Requirements:

(Ultra) high resolution pole piece

Electronic stability

Mechanical stability

Clean environment: (Ultra) high vacuum

Specimen preparation: very very thin

In general HREM is needed for studying nano-materials.

HREM examples:

Specimens:

$Ti_2Ni_{10}O_{19}$

Si

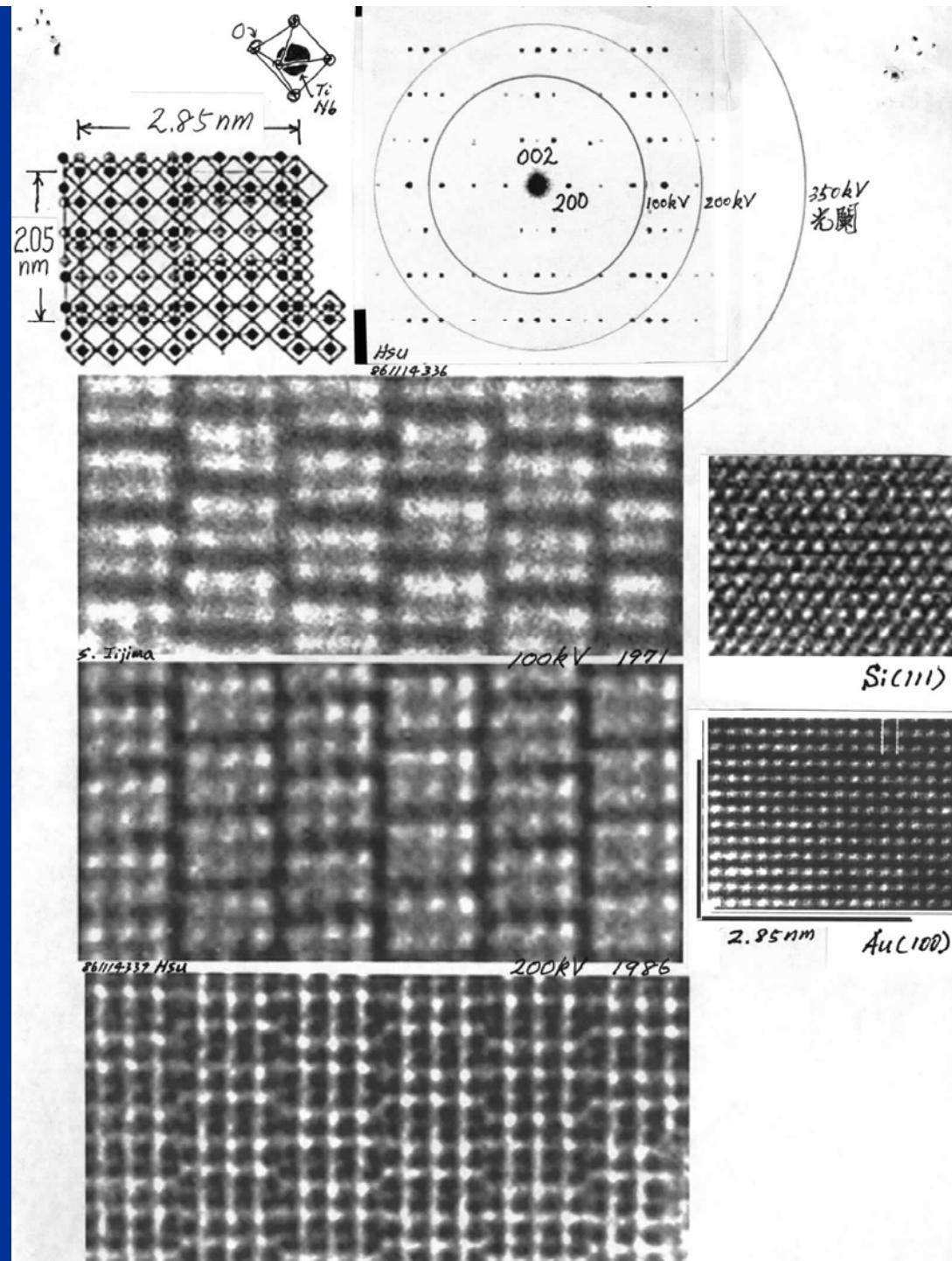
Au

Microscopes:

JEOL JEM-100B

JEOL JEM-200CX

JEOL JEM-4000EX



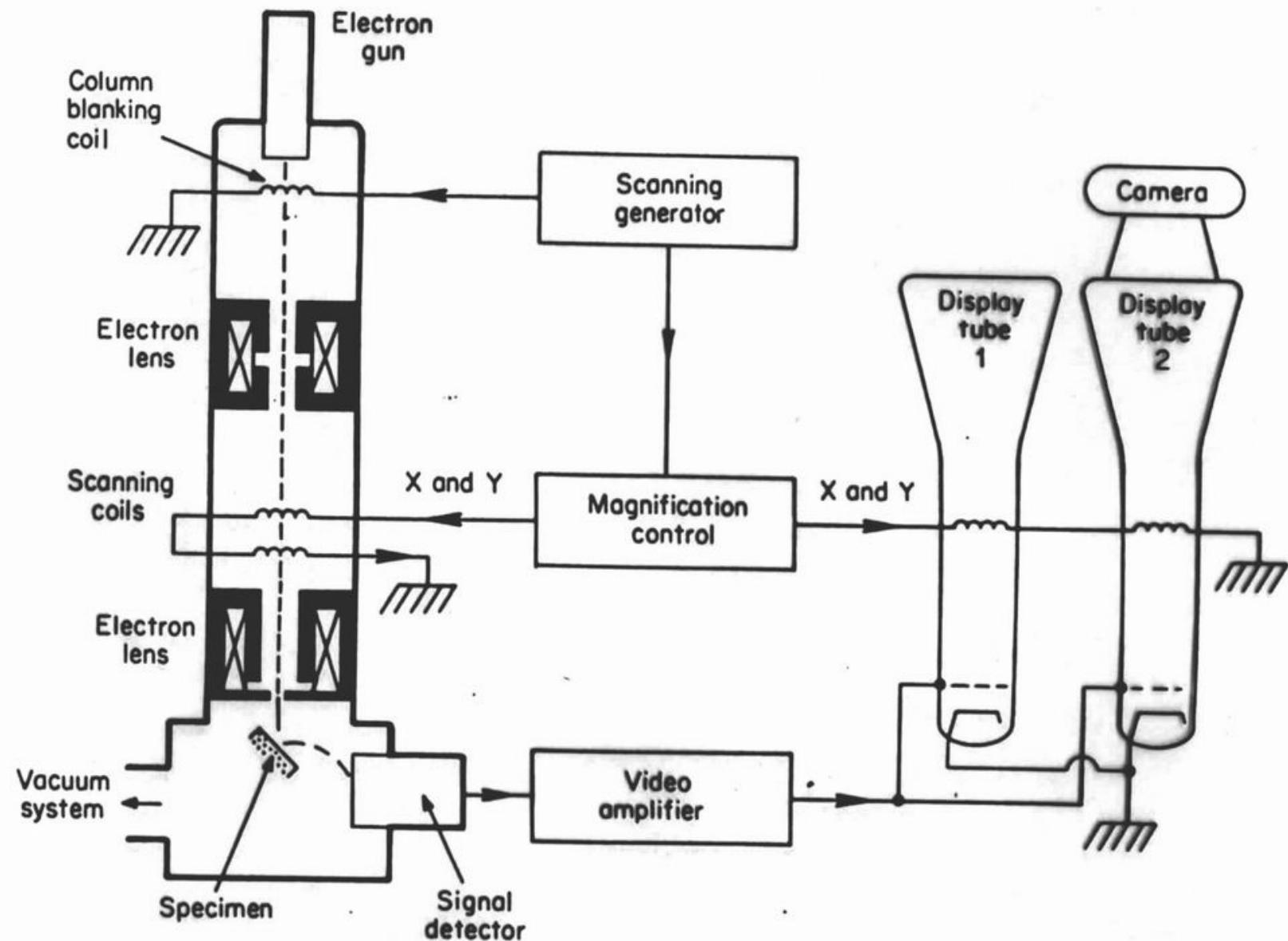
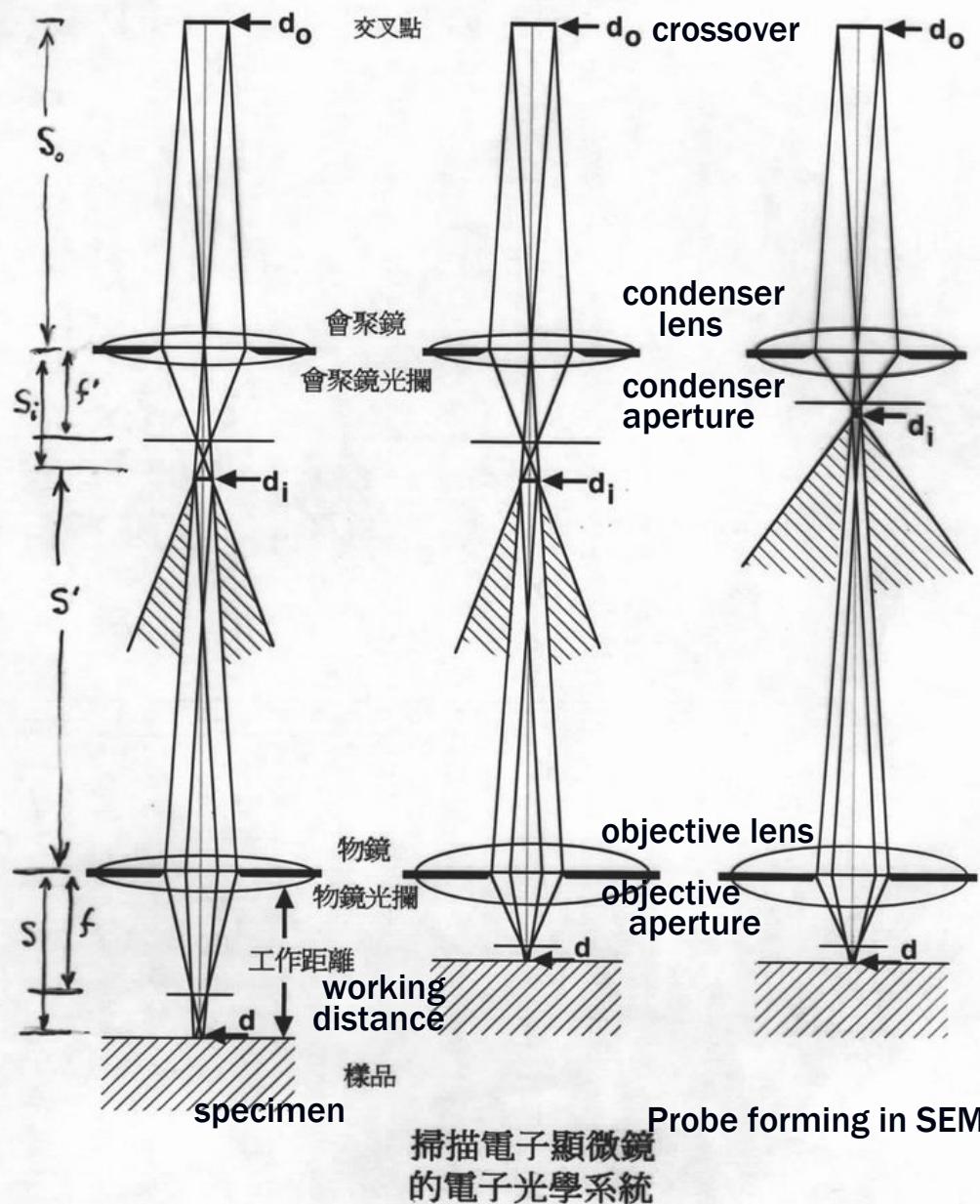


FIG. 1.2 Scanning electron microscope.



Scanning electron microscopy – microprobe

Beam/specimen interaction: When the specimen is thick, “semi-infinite”.

Monte Carlo simulation

The probe forming system:

Forming a small probe is the same as forming a small spot in the image

The column

Contrast mechanism:

Secondary electrons
Back scattered electrons
Other signals

Resolution:

Low mag: limited by scan rate
High mag: limited by lens defects – same as TEM

Detector

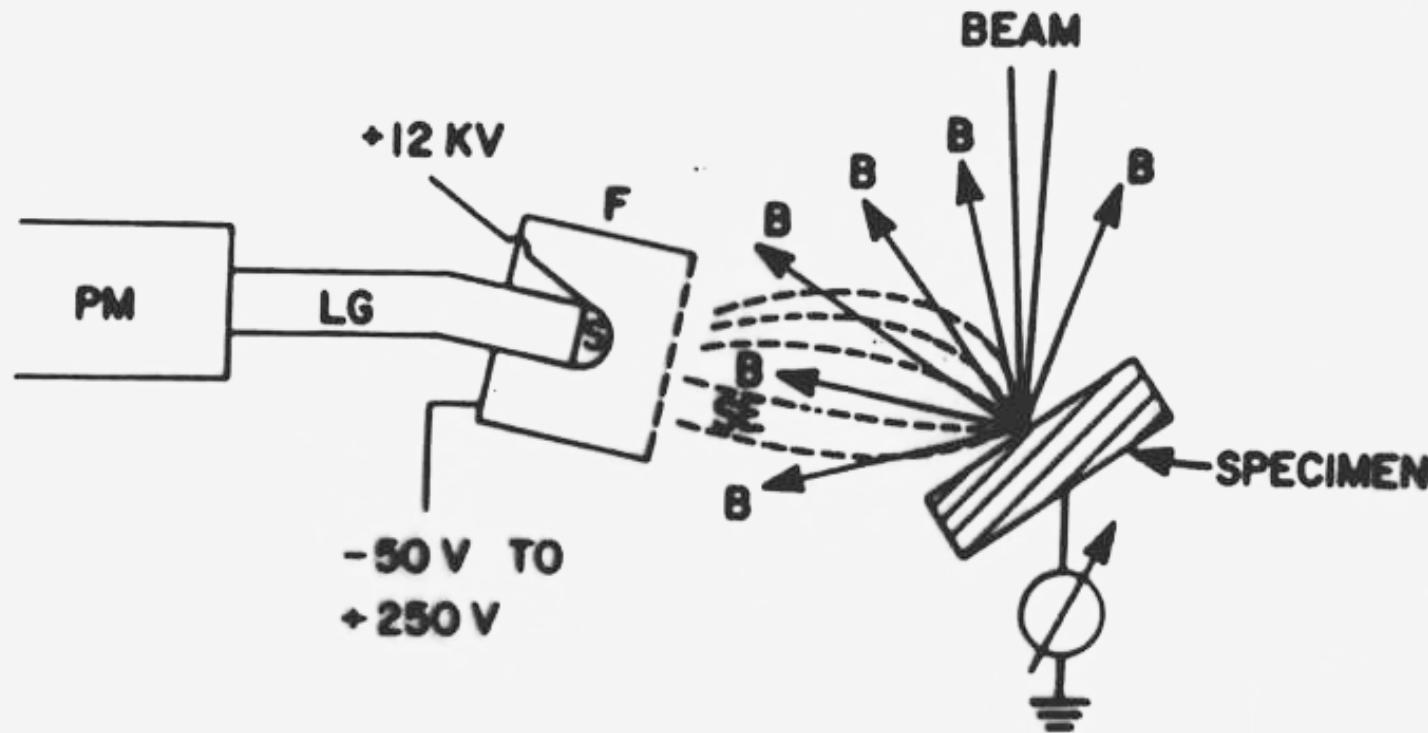
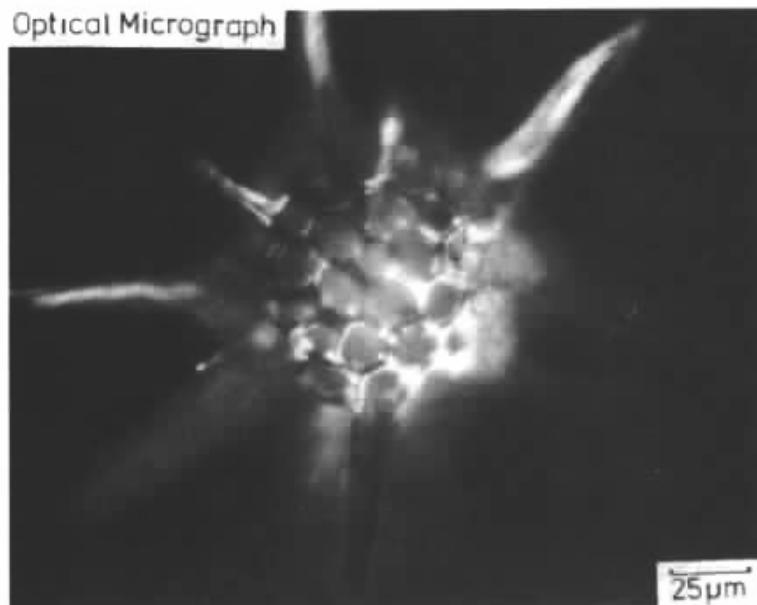


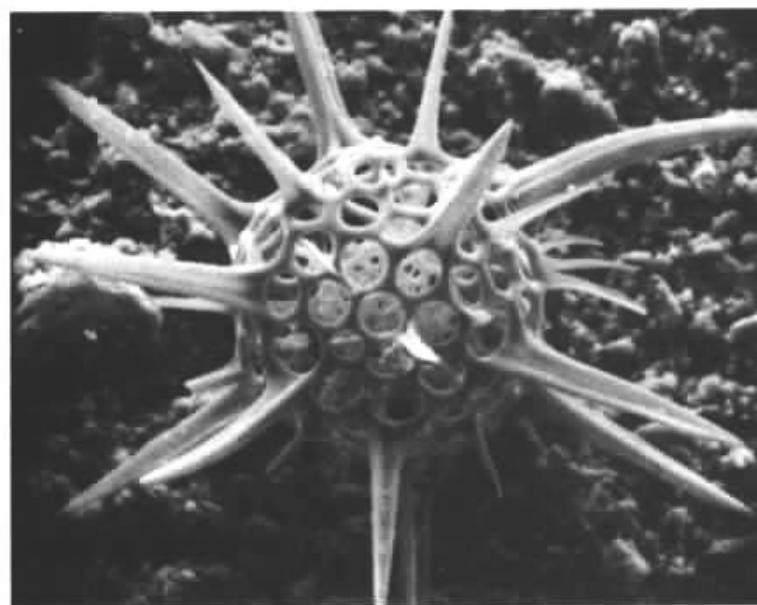
Figure 4.17. Schematic diagram of Everhart-Thornley scintillator-photomultiplier electron detector. B, backscattered electron; SE, secondary electron; F, Faraday cage; S, scintillator; LG, light guide; PM, photomultiplier.

Examples of SEM images

Optical Micrograph

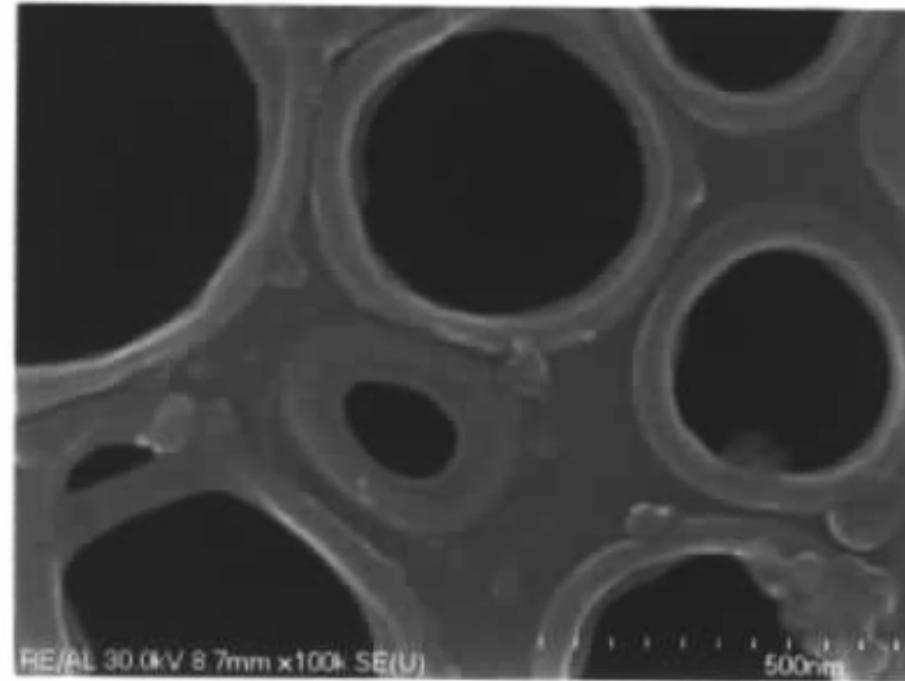


a



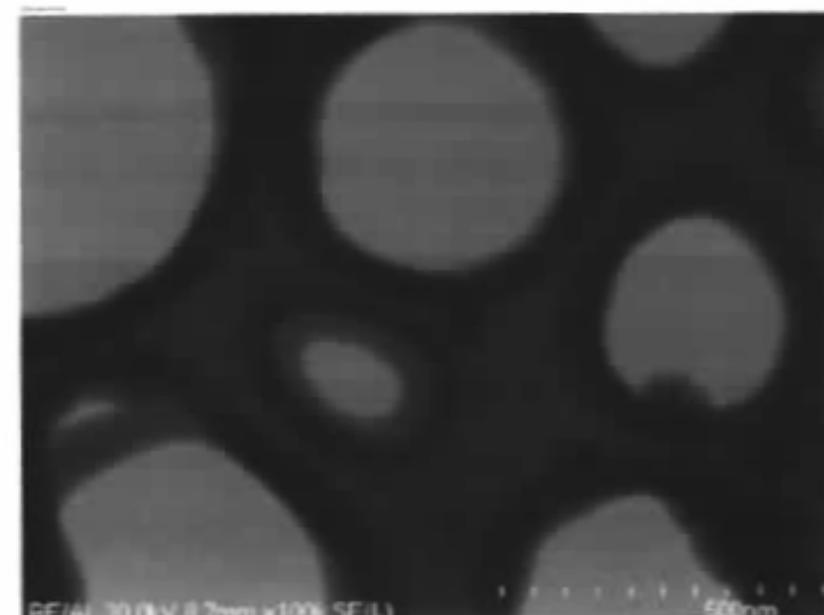
b

Figure 1.3. (a) Optical micrograph of the radiolarian *Trochodiscus longispinus*. (b) SEM micrograph of same radiolarian. The greater depth of focus and superior resolving capability of the SEM are apparent.



RE/AL 30.0kV 8.7mm x100k SE(U)

500nm



RE/AL 30.0kV 8.7mm x100k SE(L)

500nm

2001 (Hitachi S-4700)

SEM				TEM		
E (kV)	10	20	30	100	200	400
λ (A)	0.122	0.0859	0.0698	0.037	0.025	0.0126
Cs (mm)	10-20				1-3	
Resolution: beam size	$r = \lambda^{3/4} Cs^{1/4}$				image point size	
					$r = \lambda^{3/4} Cs^{1/4}$	

Electron microprobe / Analytical electron microscopy:

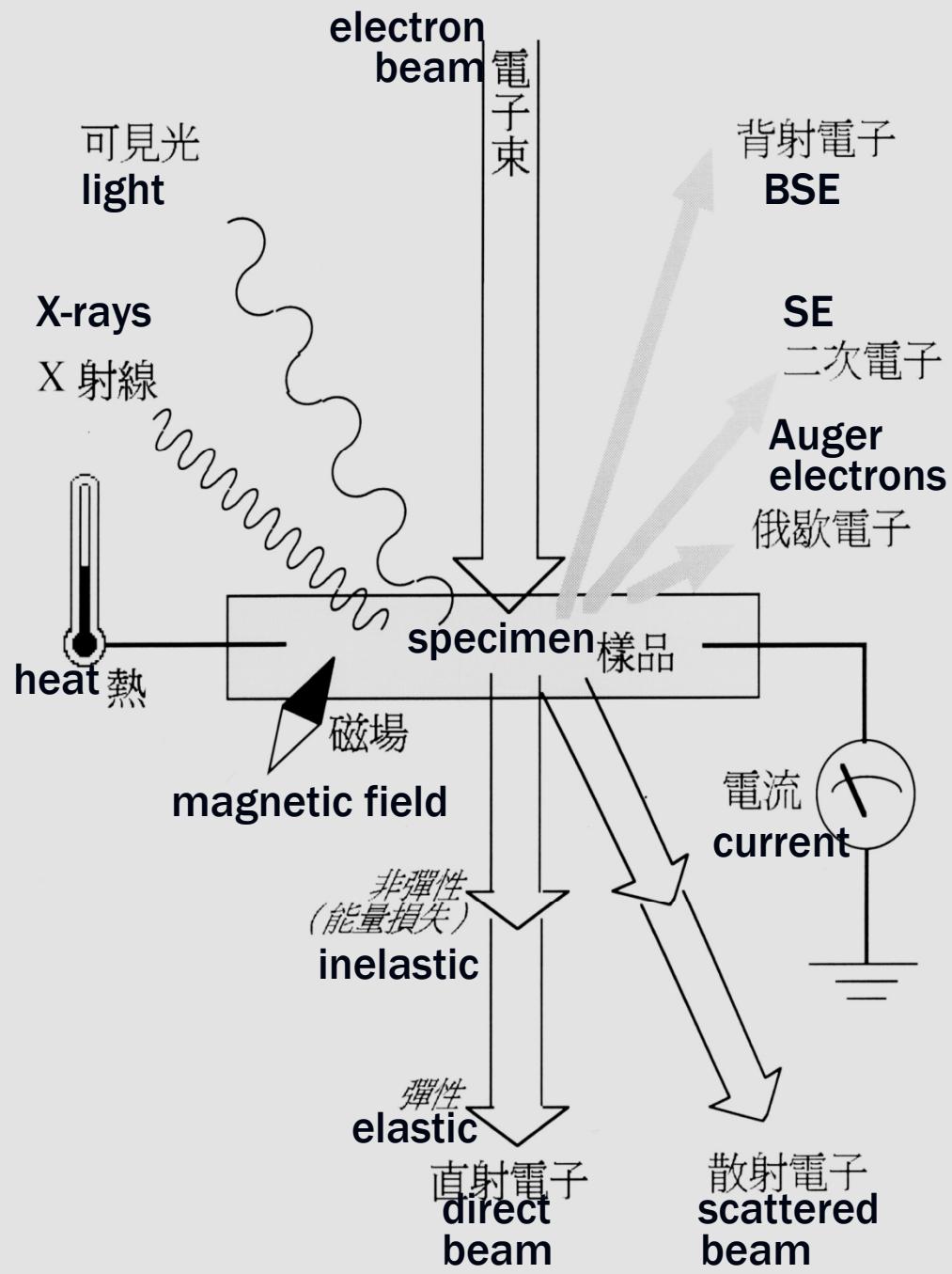
Energy dispersive (X-ray) spectrometer, EDS (EDX)

Wavelength dispersive (X-ray) spectrometer, WDS (WDX)

Electron energy loss spectroscopy, EELS

Quantitative analysis

etc.



ANALYSIS

Analytical Electron Microscopy
Electron Probe Micro Analysis (EPMA)

	Co	Ni	Te	I
Mendeleev:	A = 58.9	58.6	127.7	126.9
Moseley:	Z = 27	28	52	53

Parameter	nλ	2d	sinθ
diffraction	known	calculated	measured
spectrometry(WDS)	calculated	known	measured
spectrometry(EDS)	E: measured		

$$E = hc/\lambda, \quad \lambda = C'(Z - \sigma)^{-2} \quad (\text{for the same spectral line, K}\alpha, \text{K}\beta, \dots)$$

Instrumentation: Electron probe/microscope

Other particle beam

x-ray fluorescence

radioactive sources

WDS: X-ray optics

regular crystals \Rightarrow O and up

"soap" film crystals \Rightarrow Be and up

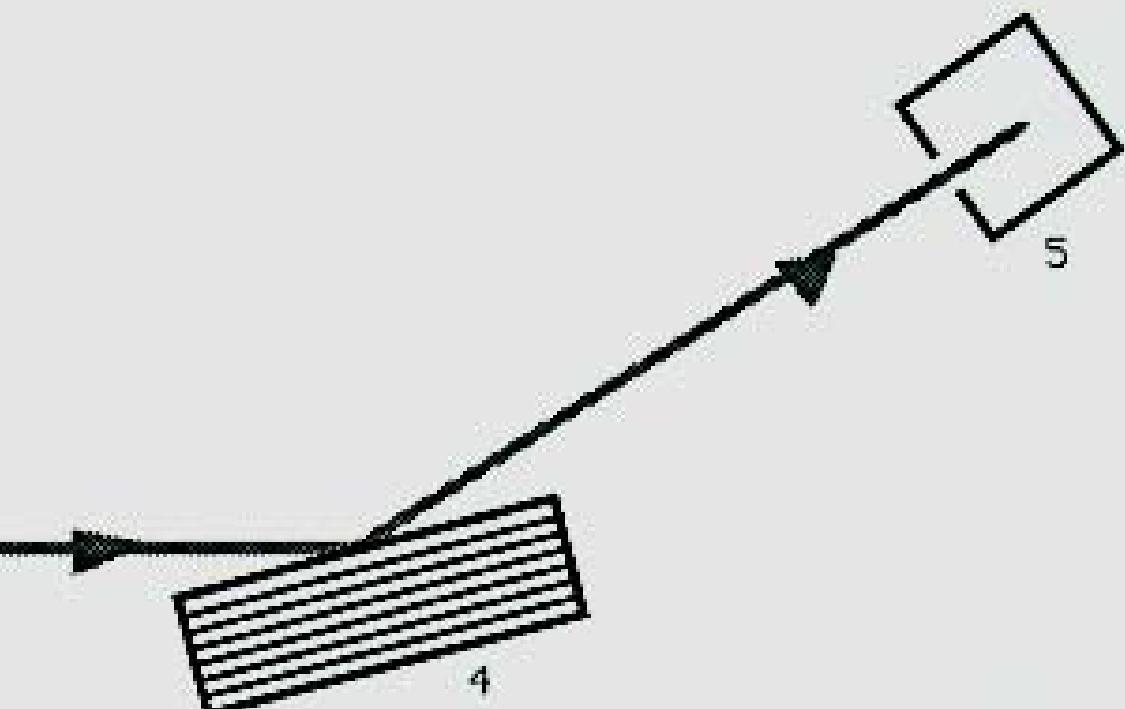
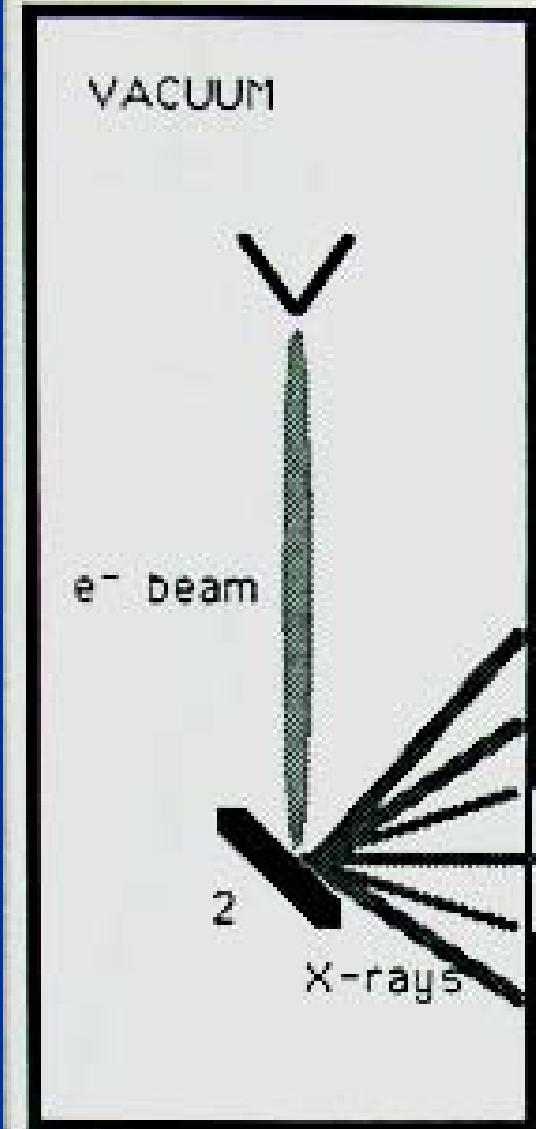
EDS: Si(Li) detector

Multi-channel analyzer (MCA)

Be window \Rightarrow Na and up

Ultra-thin window or Windowless \Rightarrow B and up

Dead layer in Si(Li) detector is the limit



1

XRD and WDS

INT

$\text{Cu K}\alpha$

$\text{Zn K}\alpha$

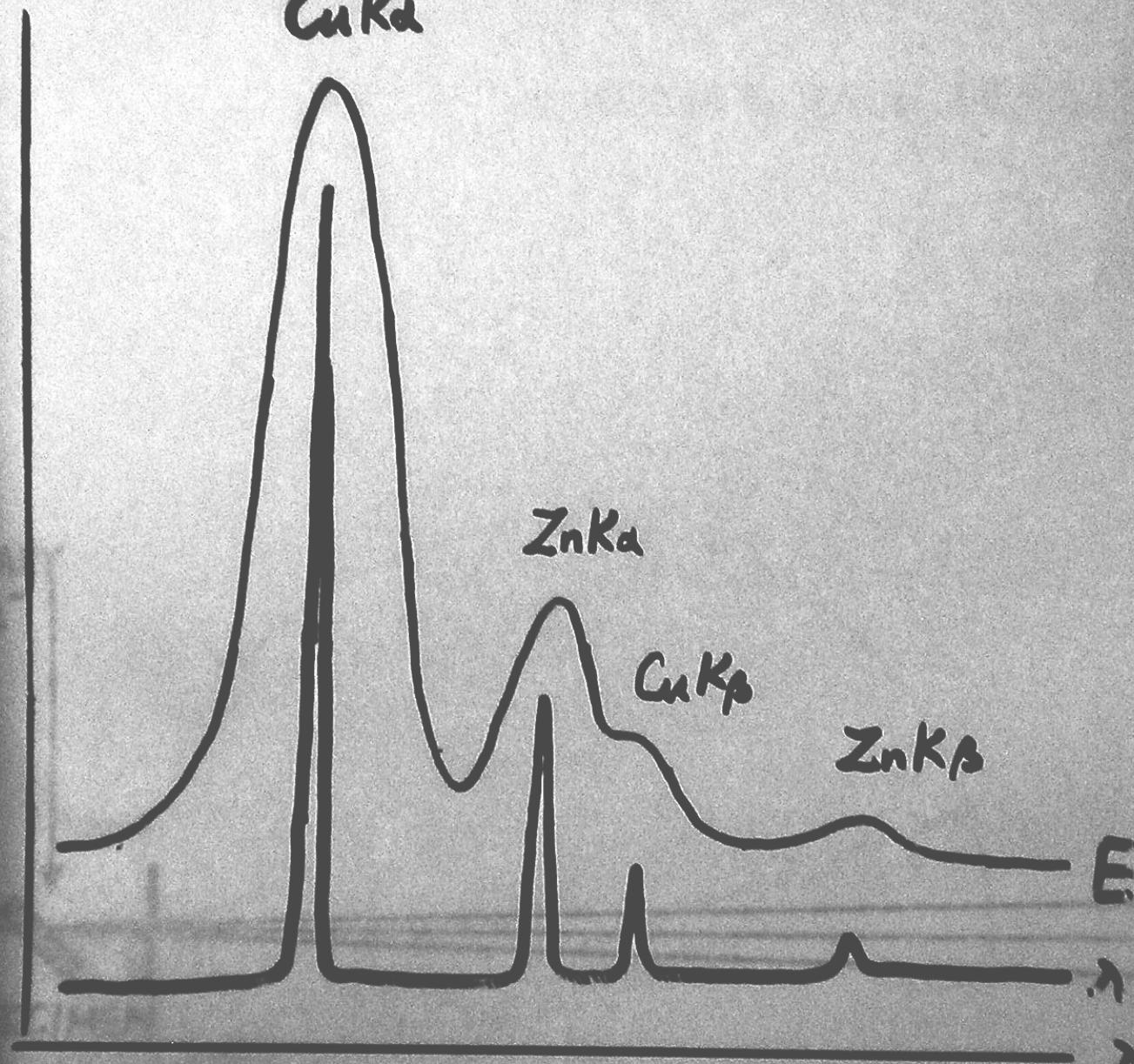
$\text{Cu K}\beta$

$\text{Zn K}\beta$

E

λ

E



Resolution

Quantitative analysis

Monte Carlo simulation

ZAF

Quantitative analysis: ZAF correction

MonteCarlo.demo

MonteCarlo demo

Quantitative analysis: ZAF correction

MonteCarlo demo

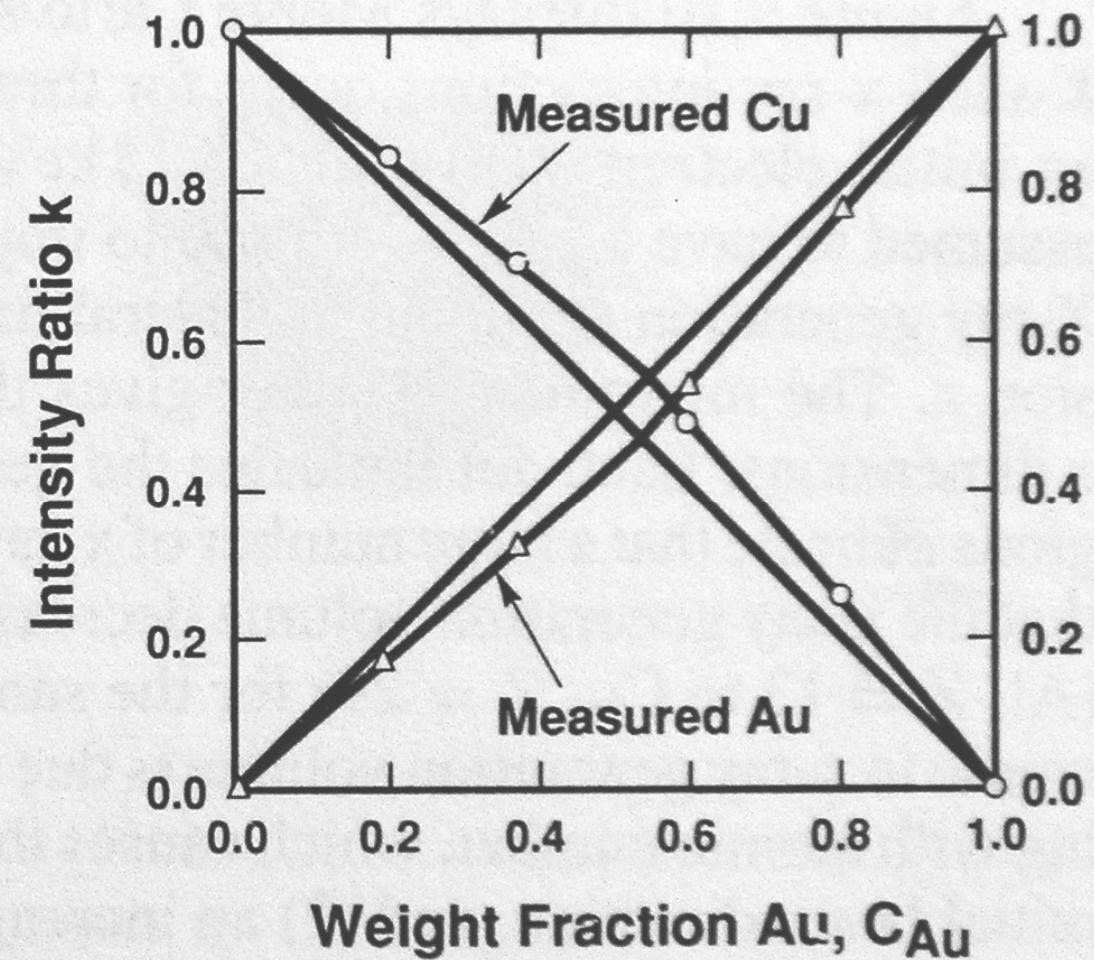


Figure 9.9. Measured Au–Cu intensity ratios k_{Au} and k_{Cu} versus the weight fraction of Au at 25 keV. Curves are measured k ratios, straight lines represent ideal behavior.

Goldstein, et al

Quantitative analysis:

ZAF correction

MonteCarlo.demo

Applications of TEM in characterization and manipulation of nano-materials

Specimen preparation: often straight forward

Observation: straight forward
beware of e-beam damage

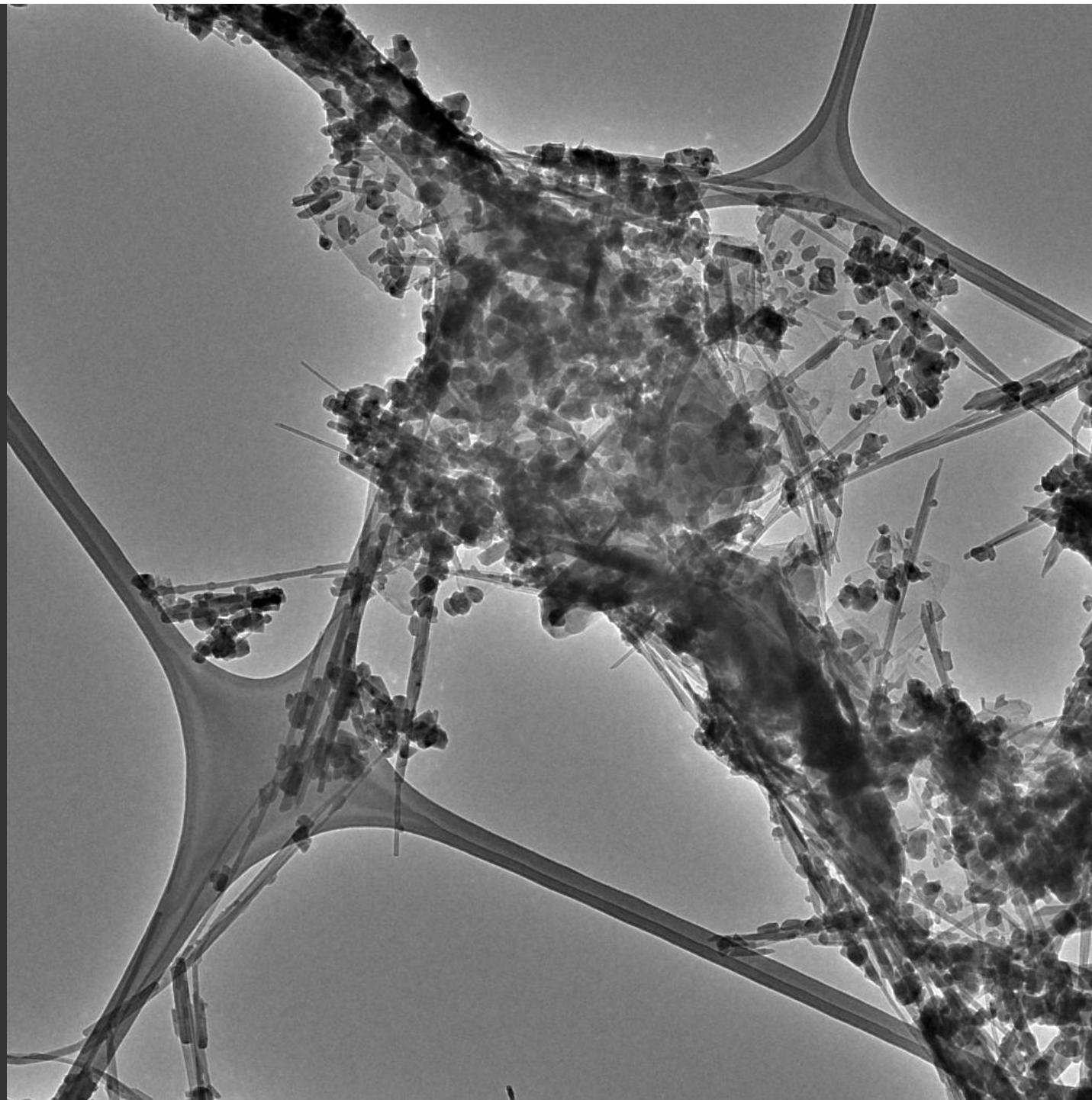
Diffraction: weak signal
orientation

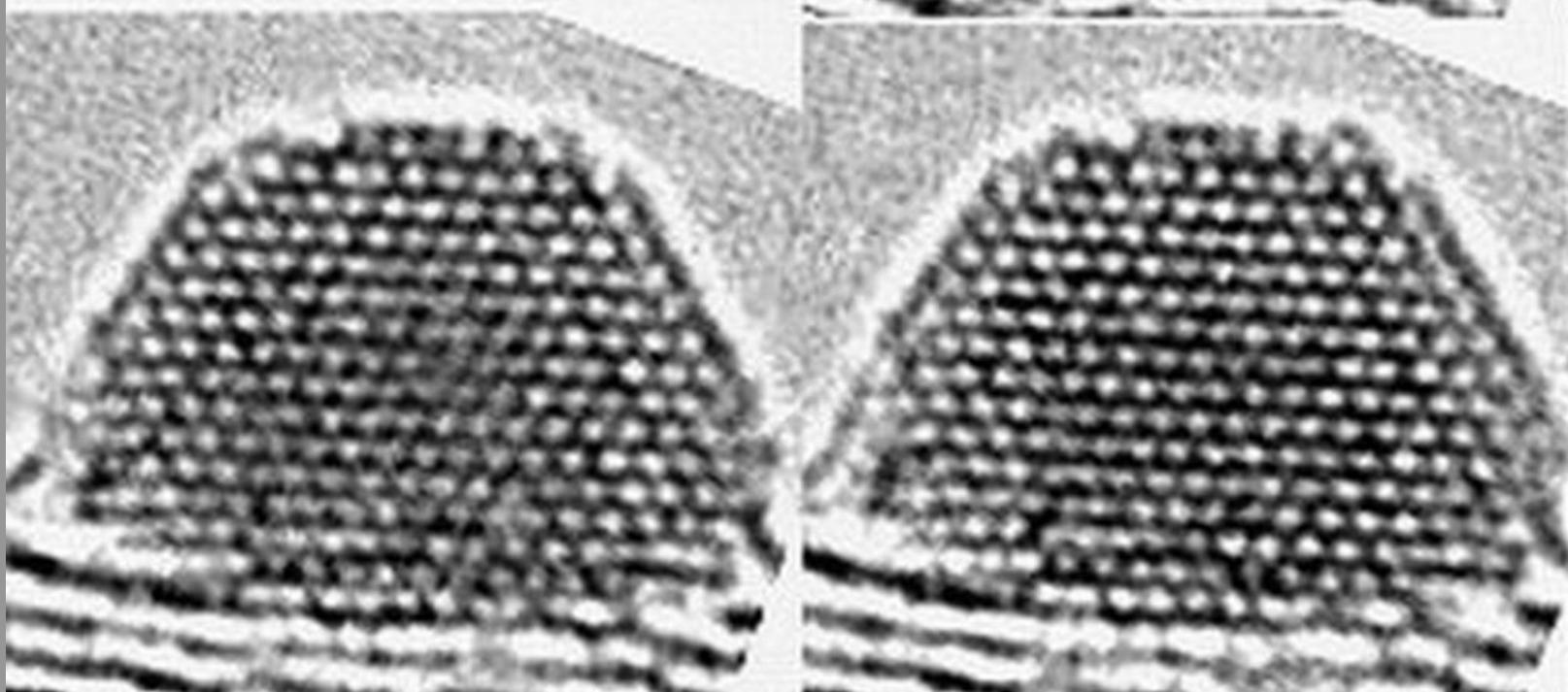
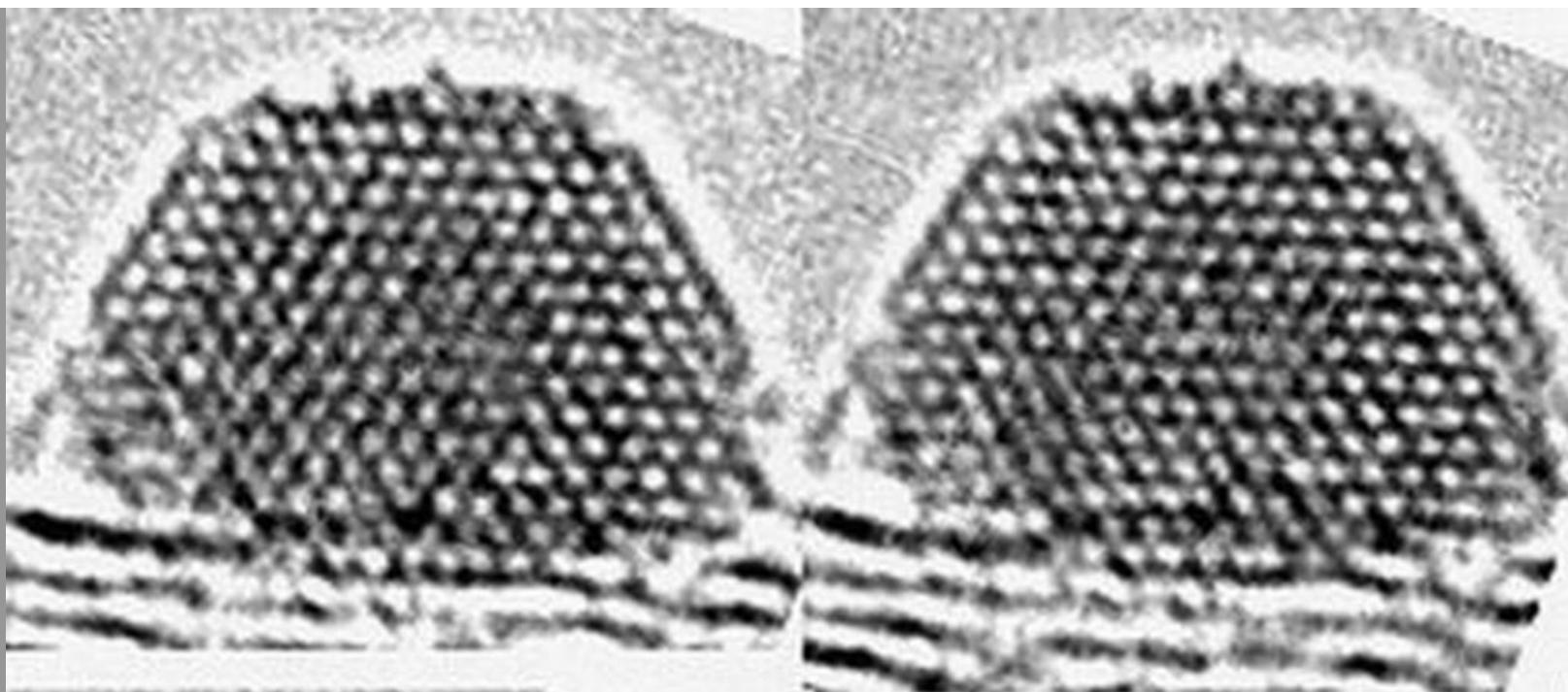
X-ray analysis: weak signal

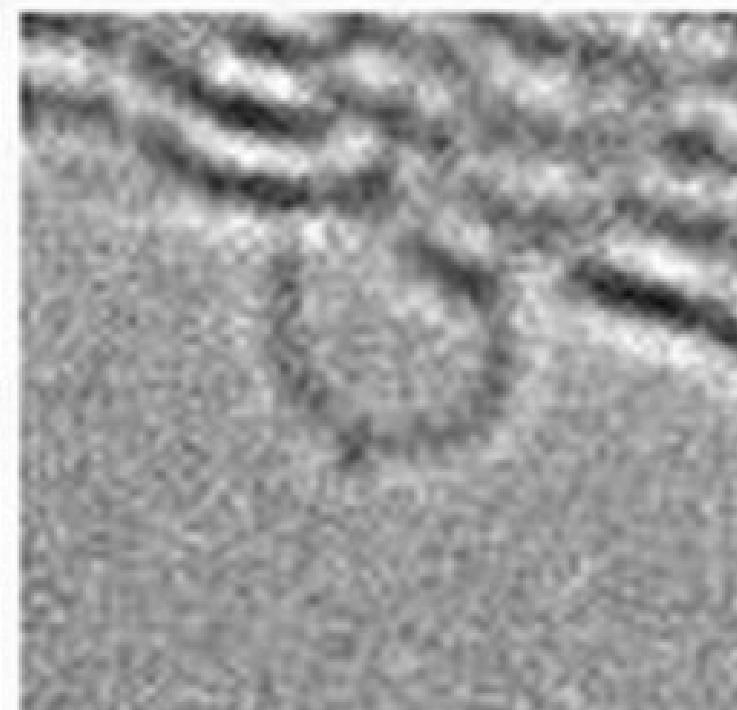
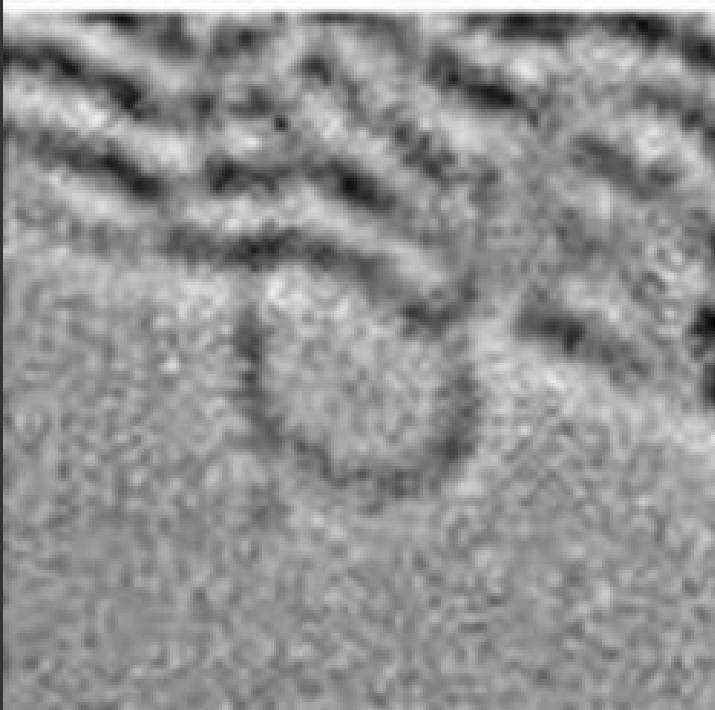
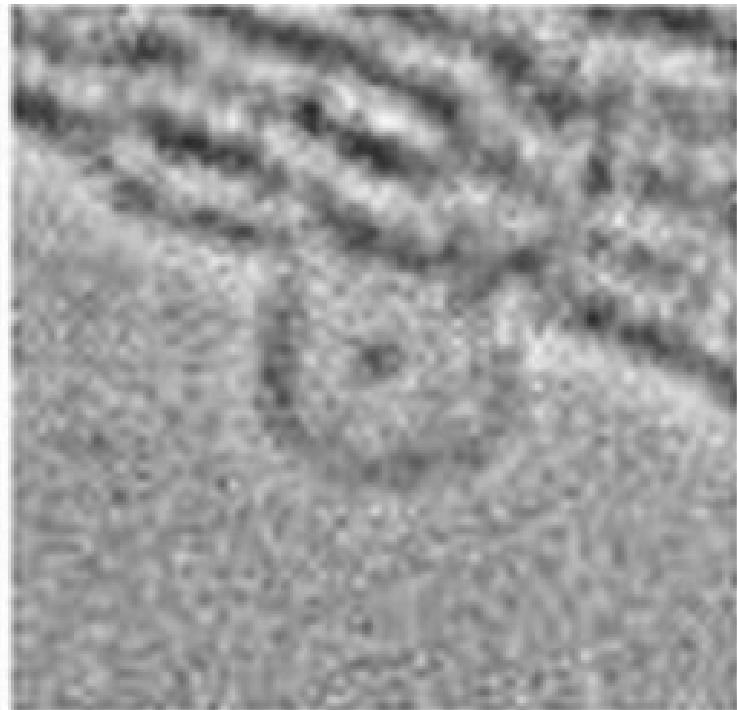
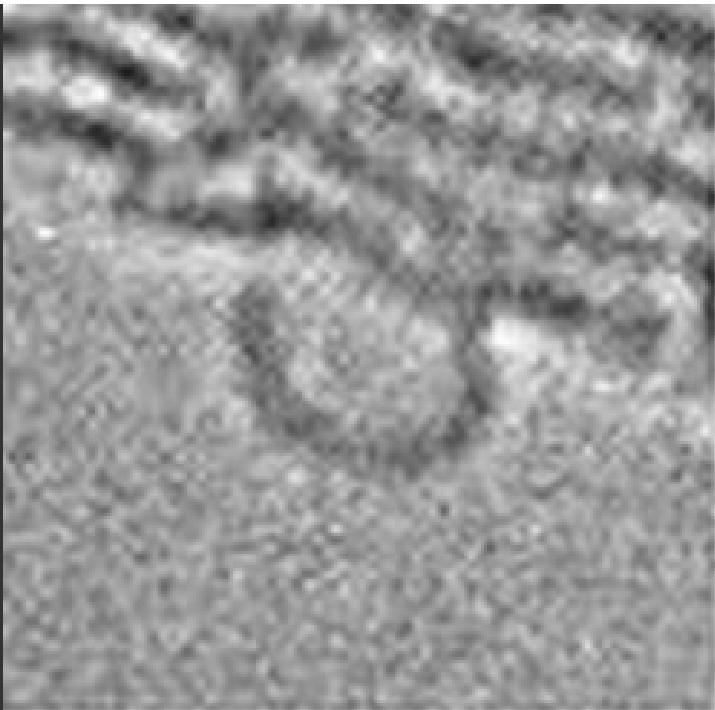
EELS: to be investigated

In situ observation of dynamical phenomena

Manipulation: mechanical
electrical
temperature
deposition, evaporation







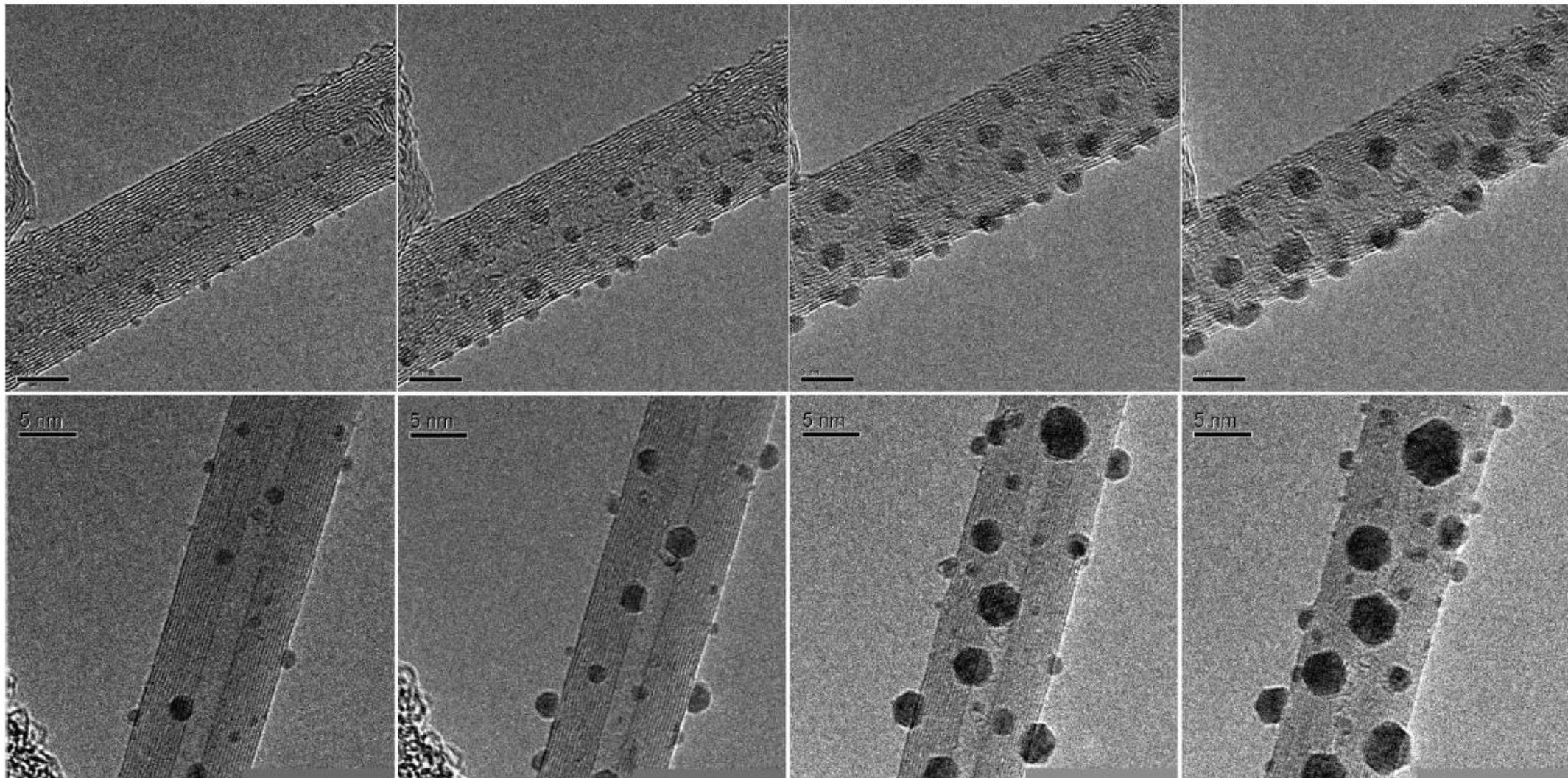


FIG. 1. Sequential TEM images of the formation of Ag clusters on the CNTs at two different temperatures. Images in the top row were taken at room temperature 296 K (heating current $I_h=0$) and those in the bottom at 503 K ($I_h=0.17$ A). From the left frame to right, the images were taken with time at about 5, 15, 35, and 55 min after Ag deposition. The scale bars are 5 nm in length.

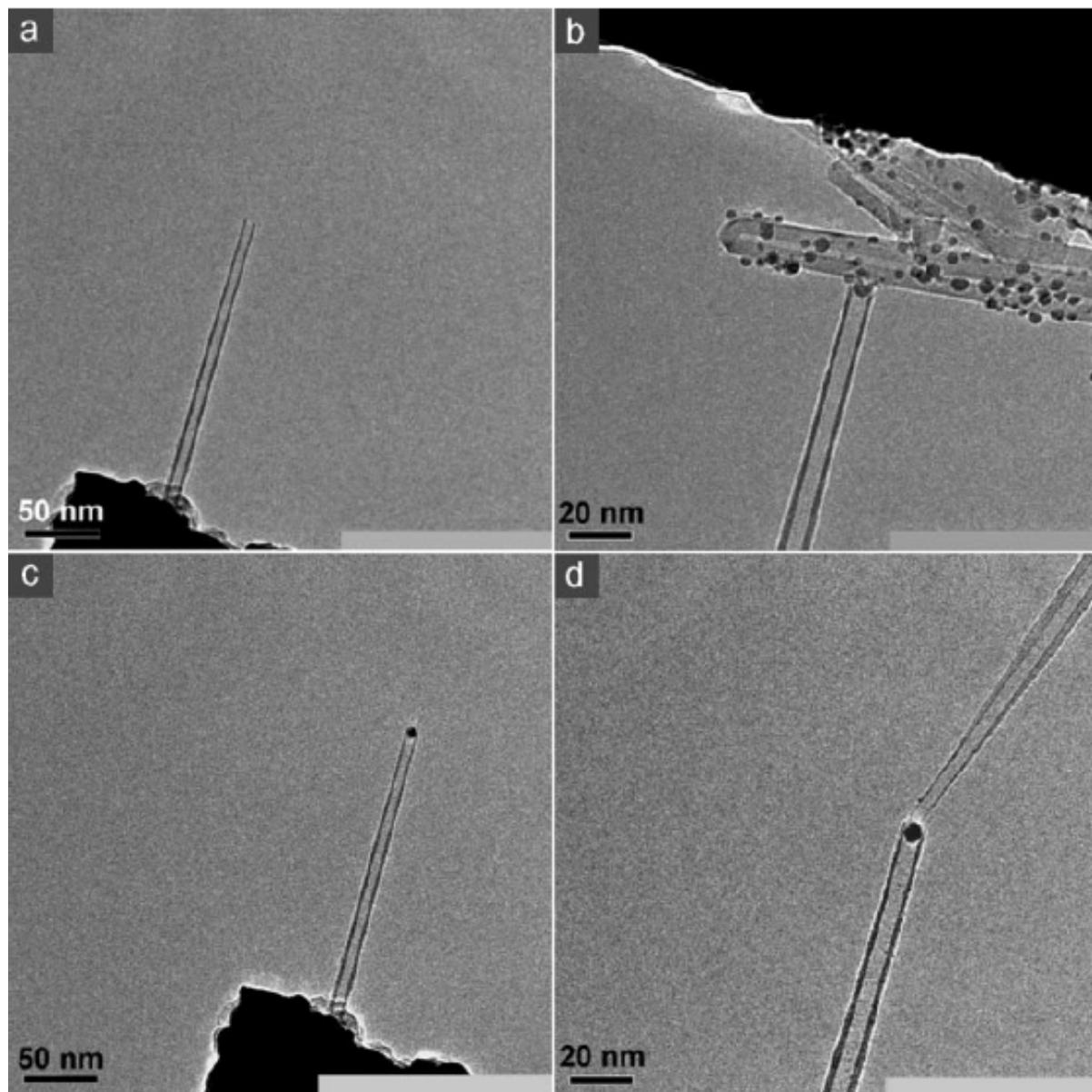


Figure 4. Transmission electron micrographs showing the insertion of Ag clusters into a peeled MWNT. a) A MWNT with a defined inner diameter ($\approx 6\text{nm}$) after the peeling process. b) This tube making contact with a chosen Ag cluster. Ag clusters of various sizes deposited on the nanotubes were formed by electron-beam evaporation under UHV. c) The Ag cluster transferred to the tube by pure mechanical force. d) The transferred Ag cluster pushed slightly into the tube by the piston rod.

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“In Situ Tailoring and Manipulation of Carbon Nanotubes”
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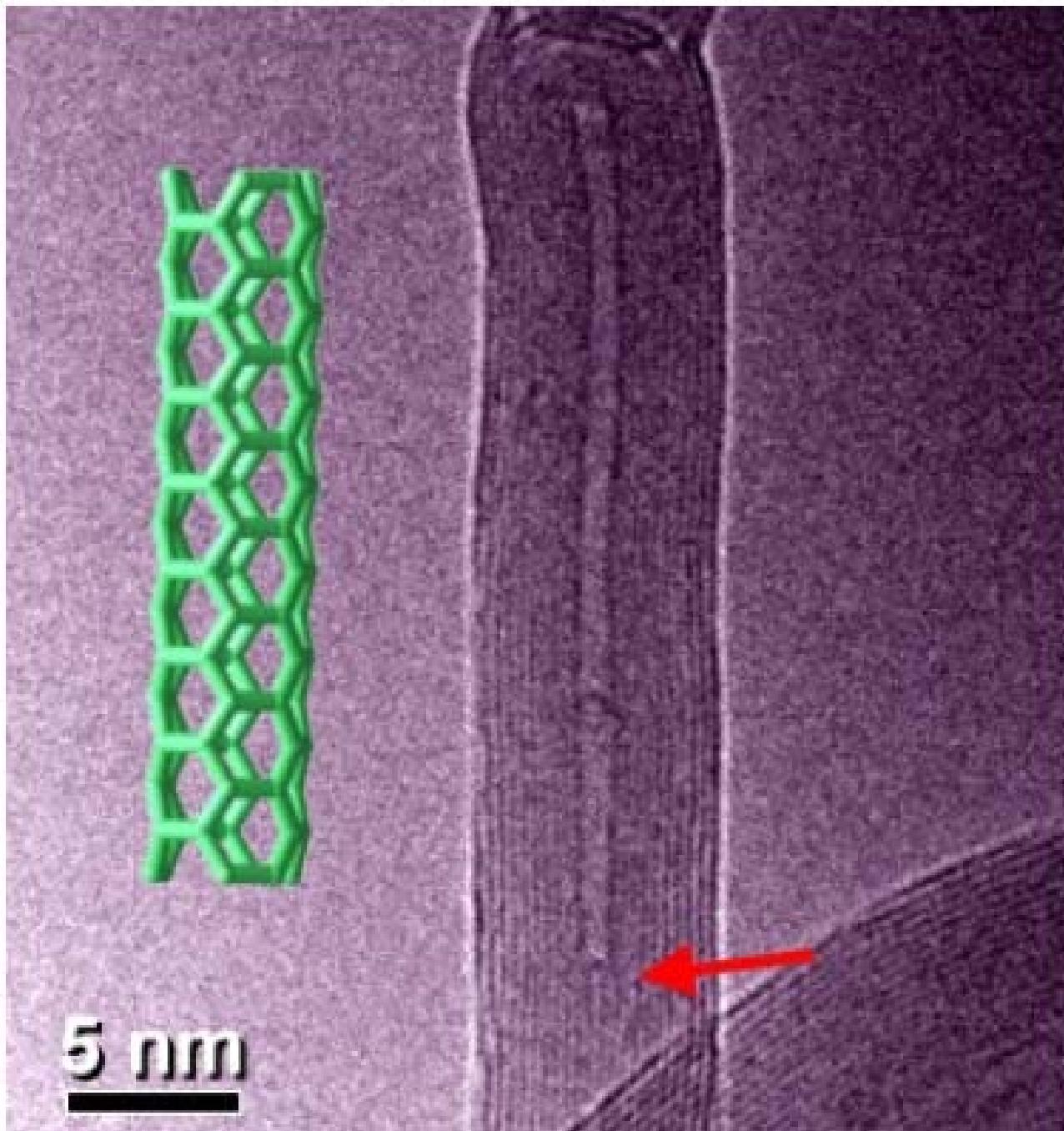


Fig. 1. Transmission electron micrograph shows the smallest SWNT formation. The smallest SWNT is arrowed. Schematic drawing is accompanied to illustrate the smallest SWNT.

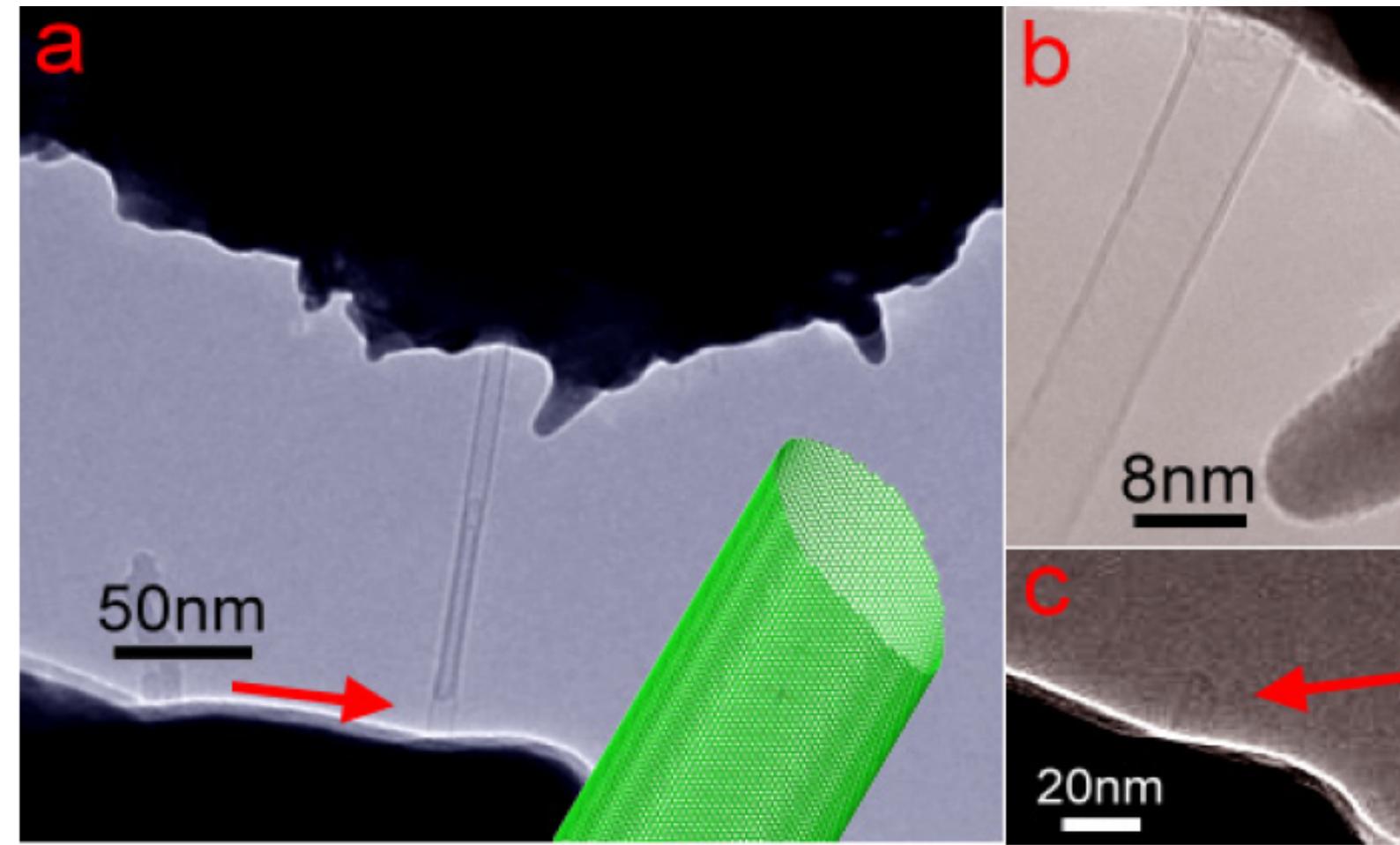
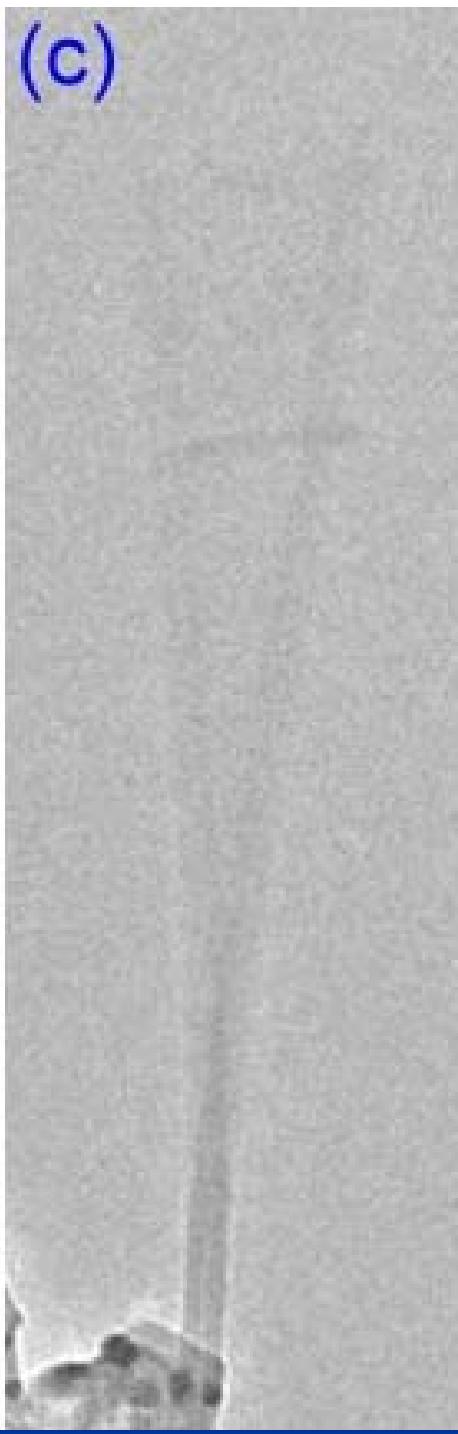
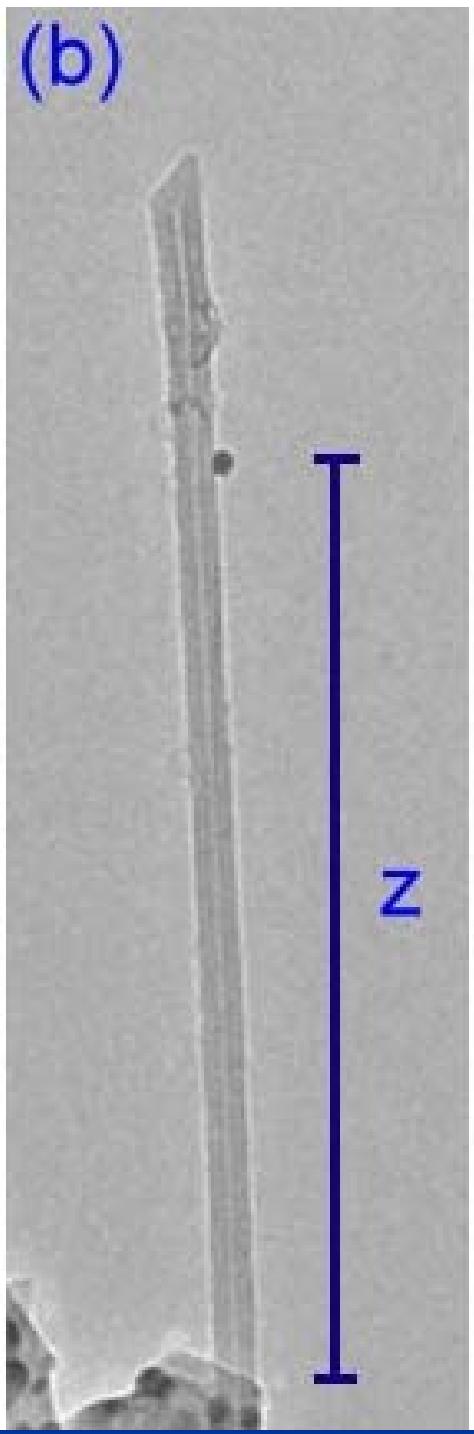
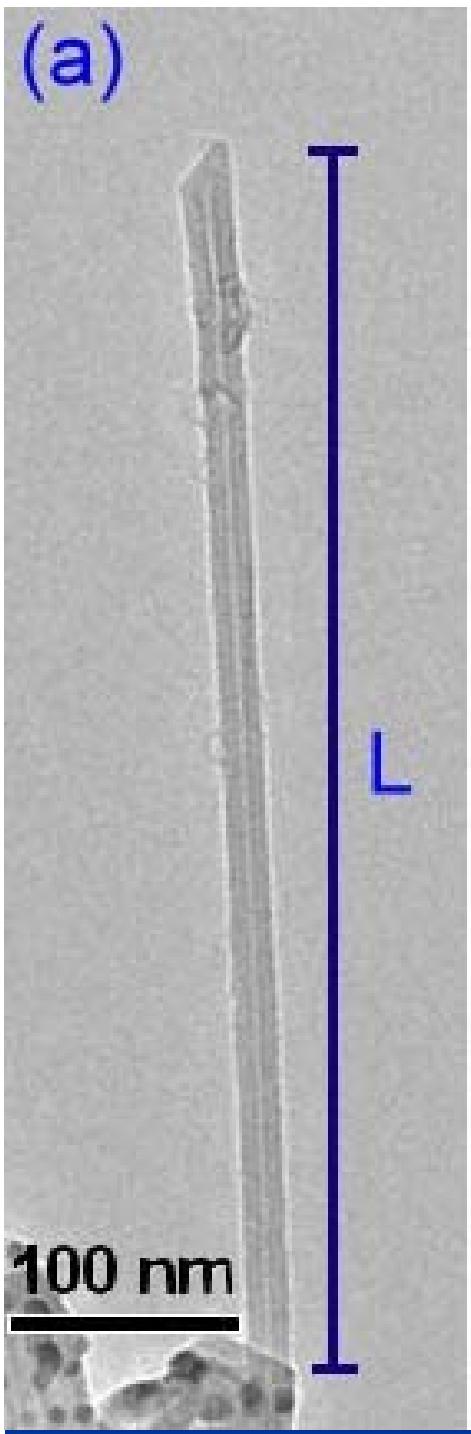
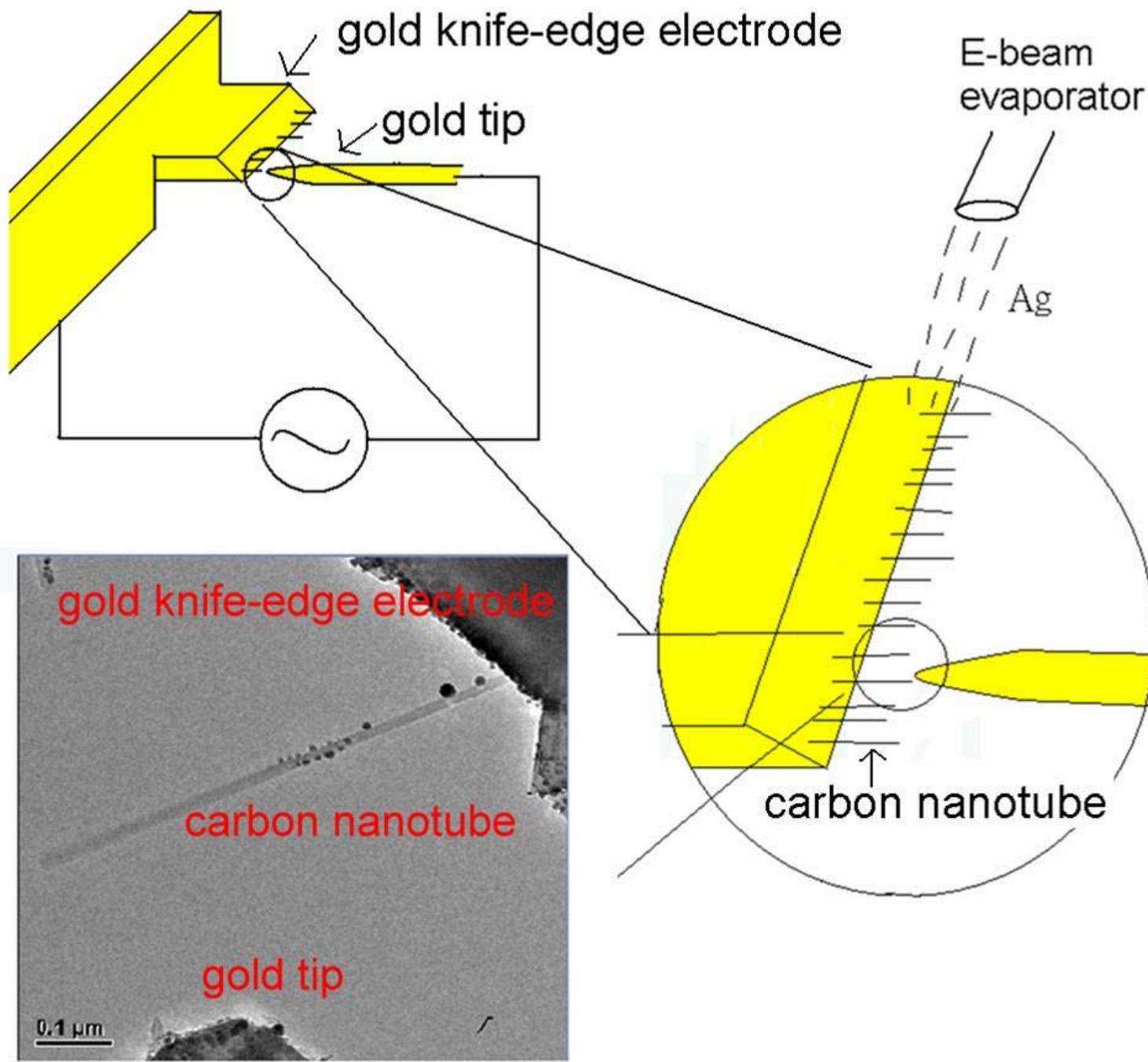
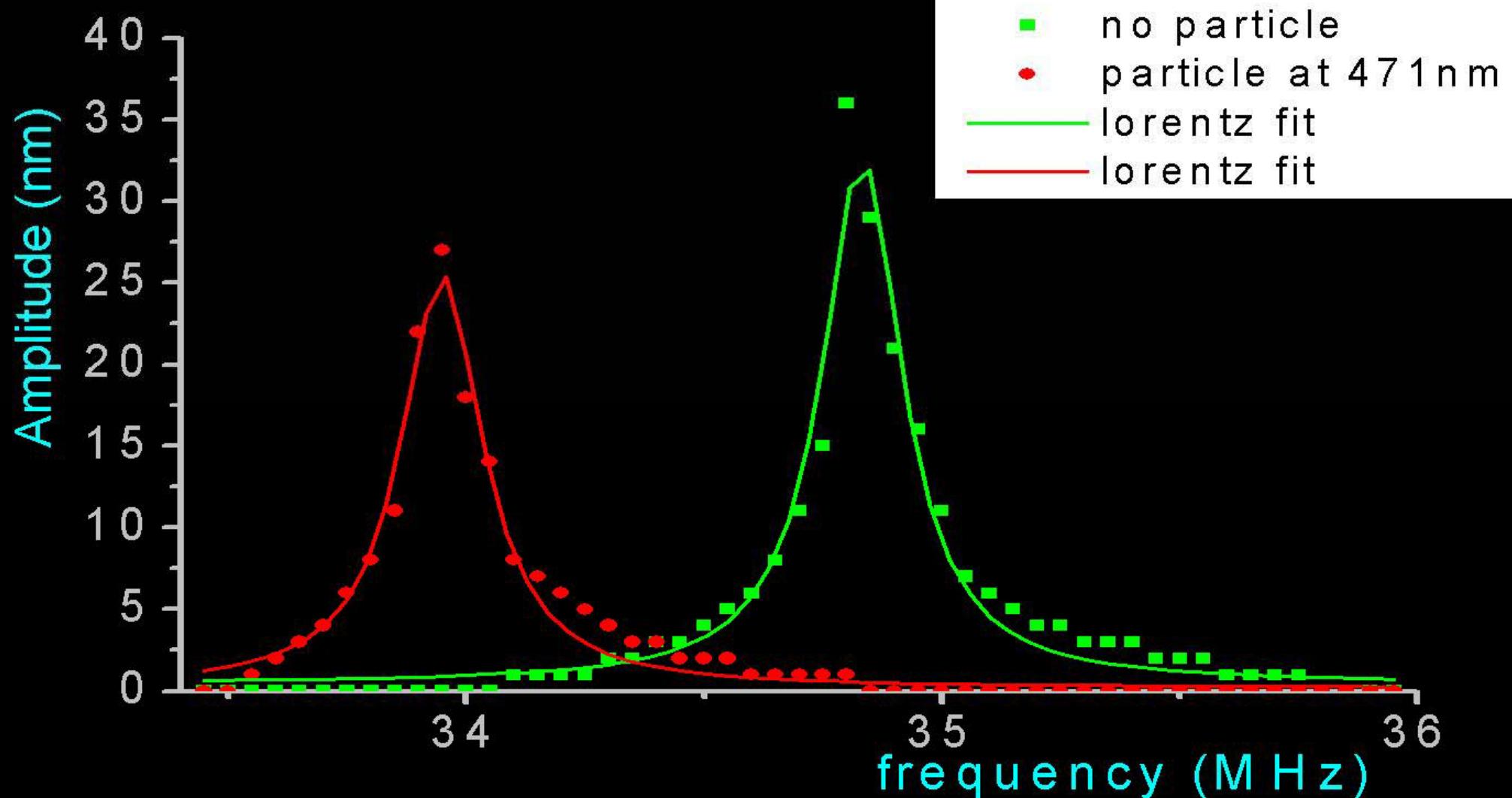


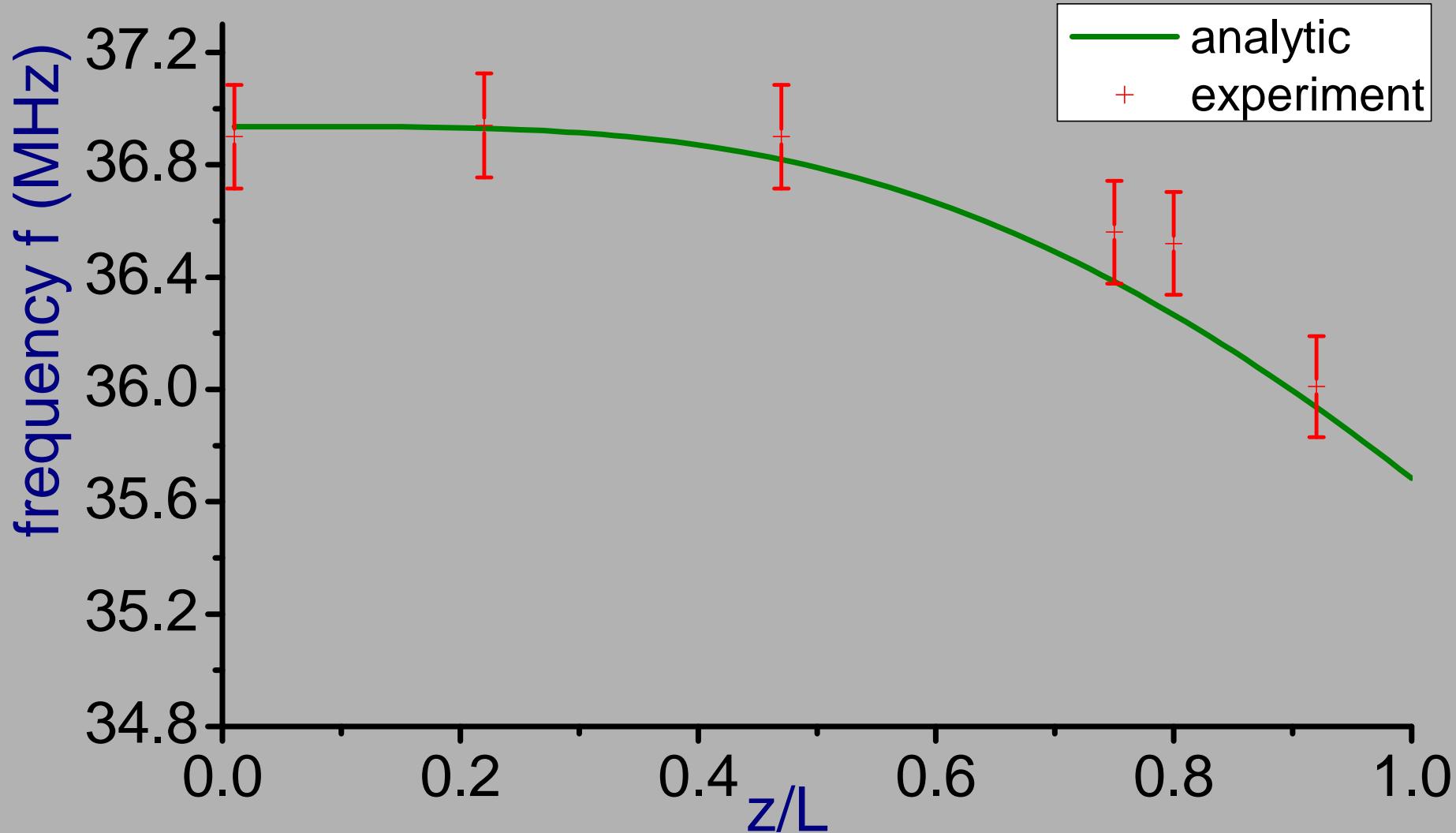
Fig. 2. Transmission electron micrographs show the largest MWNT fabrication at last stage of the extraction process. Schematic drawing is accompanied to illustrate the largest SWNT. (a) The SWNT formation (see arrow) during second internal peeling process. (b) A two-wall tube pulled out after the second peeling process. (c) The remaining SWNT on the base (see arrow) obtained by two internal peeling processes.



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Microscopy Society of America Position on Ethical Digital Imaging

RESOLUTION carried as follows: Be it resolved that the MSA position on digital image processing be approved as follows:

"Ethical digital imaging requires that the original uncompressed image file be stored on archival media (e.g., CD-R) without any image manipulation or processing operation. All parameters of the production and acquisition of this file, as well as any subsequent processing steps, must be documented and reported to ensure reproducibility.

Generally, acceptable (non-reportable) imaging operations include gamma correction, histogram stretching, and brightness and contrast adjustments. All other operations (such as Unsharp-Masking, Gaussian Blur, etc.) must be directly identified by the author as part of the experimental methodology. However, for diffraction data or any other image data that is used for subsequent quantification, all imaging operations must be reported."

MSA 2003 Summer Council Meeting Minutes